A 12 V, 15 mΩ, 4 A Integrated Power Switch with V_{IN} Lockout Select and Power Good Output

General Description

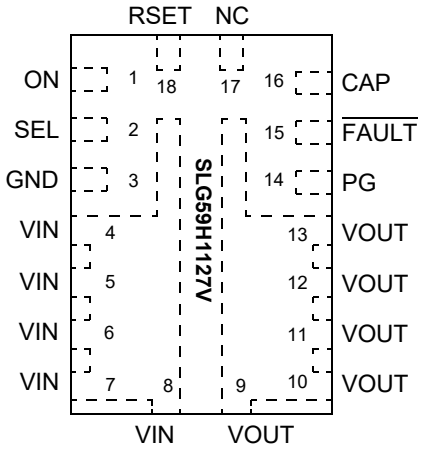
The SLG59H1127V is a high-performance, self-powered 15 mΩ nFET power switch designed for all 4.5 V to 12 V power rails up to 4 A. Using a proprietary MOSFET design, the SLG59H1127V achieves a stable 15 mΩ RDS_{ON} across a wide input voltage range. In combining novel FET design and copper pillar interconnects, the SLG59H1127V package also exhibits a low thermal resistance for high-current operation.

Designed to operate over a -40 °C to 85 °C range, the SLG59H1127V is available in a low thermal resistance, RoHS-compliant, 1.6 x 3.0 mm STQFN package.

Features

- Wide Operating Input Voltage: 4.5 V to 13.2 V
- Maximum Continuous Current: 4 A
- Automatic nFET SOA Protection
- High-performance MOSFET Switch
  - Low RDS_{ON}: 15 mΩ at V_{IN} = 12 V
  - Low $\Delta RDS_{ON}/\Delta V_{IN}$: < 0.05 mΩ/V
  - Low $\Delta RDS_{ON}/\Delta T$: < 0.06 mΩ/°C
- Capacitor-adjustable Inrush Current Control
- Two stage Current Limit Protection:
  - Resistor-adjustable Active Current Limit
  - Internal Short-circuit Current limit
- Open-drain Power Good (PG) Signaling
- Open-drain $\overline{FAULT}$ Signaling
- Fast 4 kΩ Output Discharge
- Pb-Free / Halogen-Free / RoHS Compliant Packaging

Pin Configuration

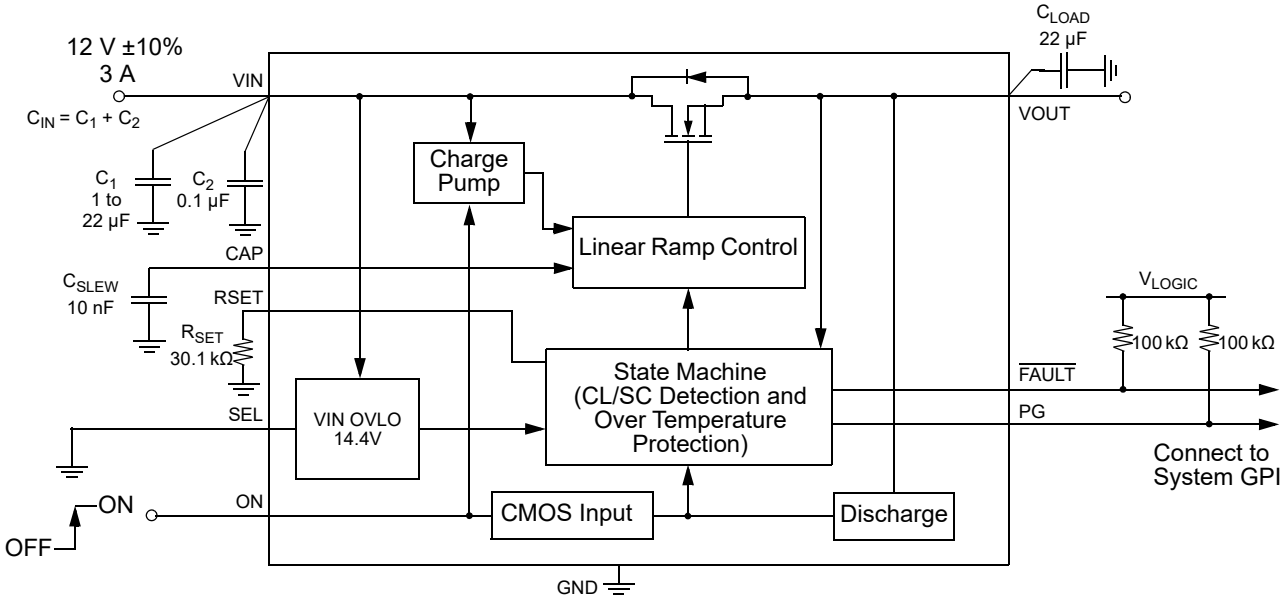


18-pin STQFN
1.6 x 3.0 mm, 0.40mm pitch
(Top View)

Applications

- Enterprise Computing & Telecom Equipment
  - 5 V and 12 V Point-of-Load Power Distribution
- PCI/PCIe Adapter Cards
- General-purpose High-voltage, Power-Rail Switching
- Multifunction Printers
- Fan Motor Control

Block Diagram



Pin Description

Pin #	Pin Name	Type	Pin Description
1	ON	Input	A low-to-high transition on this pin initiates the operation of the SLG59H1127V's state machine. ON is an asserted HIGH, level-sensitive CMOS input with ON_V_{IL} < 0.3 V and ON_V_{IH} > 0.9 V. As the ON pin input circuit does not have an internal pull-down resistor, connect this pin to a general-purpose output (GPO) of a microcontroller, an application processor, or a system controller – do not allow this pin to be open-circuited.
2	SEL	Input	Connect this pin to GND.
3	GND	GND	Pin 3 is the main ground connection for the SLG59H1127V's internal charge pump, its gate driver and current-limit circuits as well as its internal state machine. Therefore, use a short, stout connection from Pin 3 to the system's analog or power plane.
4-8	VIN	MOSFET	VIN supplies the power for the operation of the SLG59H1127V, its internal control circuitry, and the drain terminal of the nFET power switch. With 5 pins fused together at VIN, connect a 22 µF (or larger) low-ESR capacitor from this pin to ground. Capacitors used at VIN should be rated at 20 V or higher.
9-13	VOUT	MOSFET	Source terminal of n-channel MOSFET (5 pins fused for VOUT). Connect a 22 µF (or larger) low-ESR capacitor from this pin to ground. Capacitors used at VOUT should be rated at 20 V or higher.
14	PG	Output	An open-drain output, PG is asserted within TPG_{HIGH} when V_{OUT} is higher than the SLG59H1127V's $PG_{TRIGGER}$ threshold. PG output becomes deasserted within TPG_{LOW} when V_{OUT} is less than the PG_{HYS} threshold. PG is not defined for V_{IN} < 4 V.
15	$\overline{FAULT}$	Output	An open-drain output, $\overline{FAULT}$ is asserted within $T\overline{FAULT}_{LOW}$ when a V_{IN} overvoltage, a current-limit, or an over-temperature condition is detected. $\overline{FAULT}$ is deasserted within $T\overline{FAULT}_{HIGH}$ when the fault condition is removed. Connect an 100 kΩ external resistor from the $\overline{FAULT}$ pin to local system logic supply.
16	CAP	Output	A low-ESR, stable dielectric, ceramic surface-mount capacitor connected from CAP pin to GND sets the V_{OUT} slew rate and overall turn-on time of the SLG59H1127V. For best performance, the range for C_{SLEW} values are 10 nF ≤ C_{SLEW} ≤ 20 nF – please see typical characteristics for additional information. Capacitors used at the CAP pin should be rated at 10 V or higher. Please consult Applications Section on how to select C_{SLEW} based on V_{OUT} slew rate and loading conditions.
17	NC	NC	No Connect
18	RSET	Input	A 1%-tolerance, metal-film resistor between 18 kΩ and 91 kΩ sets the SLG59H1127V's active current limit. A 91 kΩ resistor sets the SLG59H1127V's active current limit to 1 A and a 18 kΩ resistor sets the active current limit to 5 A.

Ordering Information

Part Number	Type	Production Flow
SLG59H1127V	STQFN 18L FC	Industrial, -40 °C to 85 °C
SLG59H1127VTR	STQFN 18L FC (Tape and Reel)	Industrial, -40 °C to 85 °C

Absolute Maximum Ratings

Parameter	Description	Conditions	Min.	Typ.	Max.	Unit
V_{IN} to GND	Power Switch Input Voltage to GND	Continuous	-0.3	--	16	V
		Maximum pulsed V_{IN}, pulse width < 0.1 s	--	--	18	V
V_{OUT} to GND	Power Switch Output Voltage to GND		-0.3	--	V_{IN}	V
ON, SEL, CAP, RSET, PG, and $\overline{FAULT}$ to GND	ON, SEL, CAP, RSET, PG, and $\overline{FAULT}$ Pin Voltages to GND		-0.3	--	7	V
T_S	Storage Temperature		-65	--	150	°C
ESD_{HBM}	ESD Protection	Human Body Model	2000	--	--	V
ESD_{CDM}	ESD Protection	Charged Device Model	500	--	--	V
MSL	Moisture Sensitivity Level			1		
θ_{JA}	Thermal Resistance; 1.6 x 3.0 mm 18L STQFN	Determined using 1 in^2, 1 oz. copper pads under each VIN and VOUT terminal and FR4 pcb material.	--	40	--	°C/W
		Determined using 0.25 in^2, 1 oz. copper pads under each VIN and VOUT terminal and FR4 pcb material.	--	77	--	°C/W
		Determined using 0.008 in^2, 1 oz. copper pads under each VIN and VOUT terminal and FR4 pcb material.	--	125	--	°C/W
MOSFET IDS_{CONT}	Continuous Current from VIN to VOUT	T_J < 150 °C	--	--	4	A
MOSFET IDS_{PEAK}	Peak Current from VIN to VOUT	Maximum pulsed switch current, pulse width < 1 ms	--	--	6	A

Note: Stresses greater than those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Electrical Characteristics

4.5 V ≤ V_{IN} ≤ 13.2 V; C_{IN} = 22 µF, T_A = -40 °C to 85 °C, unless otherwise noted. Typical values are at T_A = 25 °C

Parameter	Description	Conditions	Min.	Typ.	Max.	Unit
V_{IN}	Operating Input Voltage		4.5	--	13.2	V
$V_{IN(OVLO)}$	V_{IN} Overvoltage Lockout Threshold	V_{IN} ↑; SEL= 0	13.5	14.4	15.2	V
$V_{IN(OVLOHYST)}$	V_{IN} Overvoltage Lockout Hysteresis		--	2	--	%
$V_{IN(UVLO)}$	V_{IN} Undervoltage Lockout Threshold	V_{IN} ↓	2.4	--	3.8	V
I_Q	Quiescent Supply Current	ON = HIGH; I_{DS} = 0 A	--	0.5	0.6	mA
I_{SHDN}	OFF Mode Supply Current	ON = LOW; I_{DS} = 0 A	--	1	3	µA
RDS_{ON}	ON Resistance	T_A = 25°C; I_{DS} = 0.1 A	--	15	18	mΩ
		T_A = 85°C; I_{DS} = 0.1 A	--	22	24	mΩ
MOSFET IDS	Current from VIN to VOUT	Continuous	--	--	4	A

Electrical Characteristics (continued)

4.5 V ≤ V_{IN} ≤ 13.2 V; C_{IN} = 22 µF, T_A = -40 °C to 85 °C, unless otherwise noted. Typical values are at T_A = 25 °C

Parameter	Description	Conditions	Min.	Typ.	Max.	Unit
I_{LIMIT}	Active Current Limit, I_{ACL}	V_{OUT} > 0.5 V; R_{SET} = 30.1 kΩ	2.8	3.2	3.6	A
	Short-circuit Current Limit, I_{SCL}	V_{OUT} < 0.5 V	--	0.5	--	A
T_{ACL}	Active Current Limit Response Time		--	120	--	µs
$R_{DISCHRG}$	Output Discharge Resistance		3.5	4.4	5.3	kΩ
C_{LOAD}	Output Load Capacitance	C_{LOAD} connected from VOUT to GND	--	22	--	µF
T_{ON_Delay}	ON Delay Time	50% ON to 10% V_{OUT} ↑; V_{IN} = 4.5 V; C_{SLEW} = 10 nF; R_{LOAD} = 100 Ω, C_{LOAD} = 10 µF	--	0.4	0.5	ms
		50% ON to 10% V_{OUT} ↑; V_{IN} = 12 V; C_{SLEW} = 10 nF; R_{LOAD} = 100 Ω, C_{LOAD} = 10µF	--	0.7	0.9	ms
T_{Total_ON}	Total Turn ON Time	50% ON to 90% V_{OUT} ↑	Set by External C_{SLEW}[1]			ms
		50% ON to 90% V_{OUT} ↑; V_{IN} = 4.5 V; C_{SLEW} = 10 nF; R_{LOAD} = 100 Ω, C_{LOAD} = 10 µF	--	1.6	2.1	ms
		50% ON to 90% V_{OUT} ↑; V_{IN} = 12 V; C_{SLEW} = 10 nF; R_{LOAD} = 100 Ω, C_{LOAD} = 10 µF	--	4	6	ms
$V_{OUT(SR)}$	V_{OUT} Slew rate	10% V_{OUT} to 90% V_{OUT} ↑	Set by External C_{SLEW}[1]			V/ms
		10% V_{OUT} to 90% V_{OUT} ↑; V_{IN} = 4.5 V to 12 V; C_{SLEW} = 10 nF; R_{LOAD} = 100 Ω, C_{LOAD} = 10 µF	2.7	3.2	3.9	V/ms
T_{OFF_Delay}	OFF Delay Time	50% ON to V_{OUT} Fall Start ↓; V_{IN} = 4.5 V to 12 V; R_{LOAD} = 100 Ω, No C_{LOAD}	--	15	--	µs
T_{FALL}	V_{OUT} Fall Time	90% V_{OUT} ↓ to 10% V_{OUT} ↓ V_{IN} = 4.5 V to 12 V; R_{LOAD} = 100 Ω, No C_{LOAD}	10.4	12.7	25	µs
$T\overline{FAULT}_{LOW}$	$\overline{FAULT}$ Assertion Time	Abnormal Step Load Current event to Fault↓ I_{ACL} = 1 A; V_{IN} = 12 V; R_{SET} = 91 kΩ; switch in 10 Ω load;	--	80	--	µs
$T\overline{FAULT}_{HIGH}$	$\overline{FAULT}$ De-assertion Time	Delay to FAULT↑ after fault condition is removed; I_{ACL} = 1 A; V_{IN} = 12 V; R_{SET} = 91 kΩ; switch out 10 Ω load	--	180	--	µs
$\overline{FAULT}_{VOL}$	$\overline{FAULT}$ Output Low Voltage	$I_{\overline{FAULT}}$ = 1 mA	--	0.2	--	V
$V_{PG(OL)}$	PG Pin Output Low Voltage	V_{LOGIC} = 5 V, $I_{PG(OL)}$ = -0.1 mA	--	--	0.4	V
$V_{PG(OH)}$	PG Pin Output High Voltage	V_{LOGIC} = 5 V, $I_{PG(OH)}$ = 0.1 mA	V_{LOGIC} - 0.4	--	V_{LOGIC}	V
$PG_{TRIGGER}$	Power Good Threshold Voltage Level	V_{OUT} % of V_{IN}	86	90	94	%

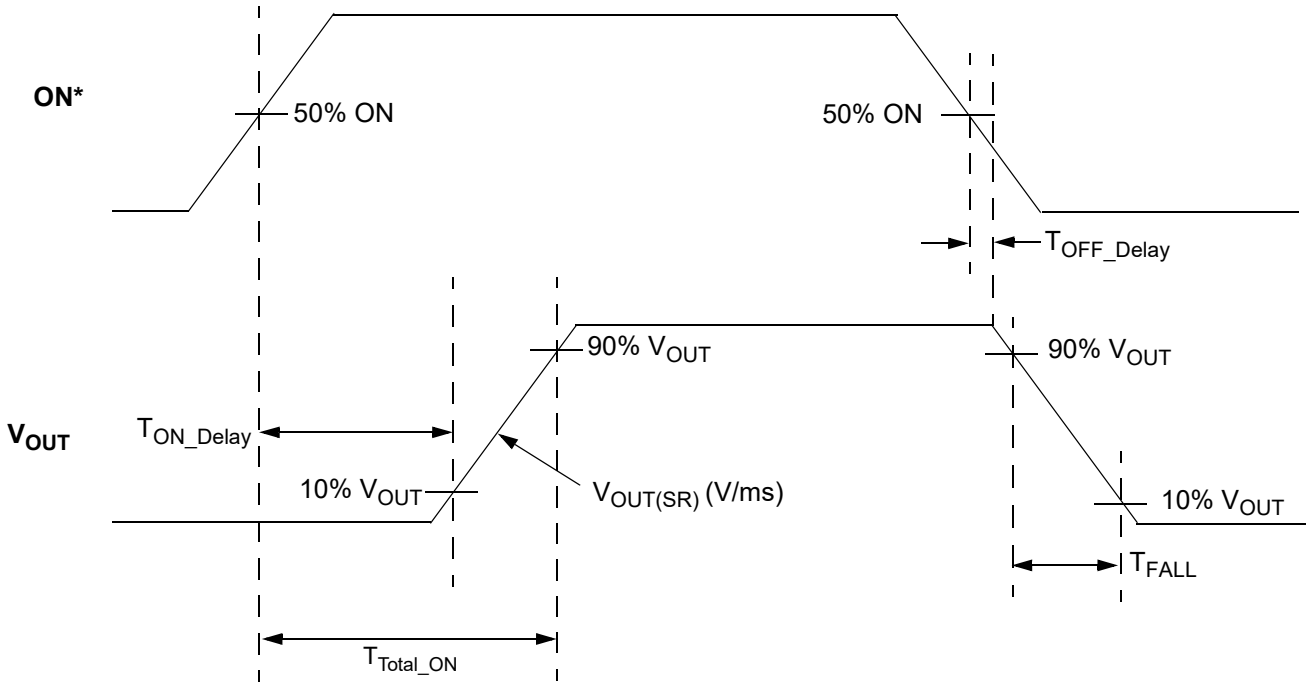
Electrical Characteristics (continued)

4.5 V ≤ V_{IN} ≤ 13.2 V; C_{IN} = 22 µF, T_A = -40 °C to 85 °C, unless otherwise noted. Typical values are at T_A = 25 °C

Parameter	Description	Conditions	Min.	Typ.	Max.	Unit
PG_{HYS}	Power Good Hysteresis ↓	V_{OUT} ↓ % of V_{IN}	81	85	89	%
TPG_{HIGH}	PG Assertion Time	Delay to PG↑ after $PG_{TRIGGER}$ threshold is crossed.	1	1.25	1.5	ms
TPG_{LOW}	PG De-assertion Time	Delay to PG↓ after $PG_{TRIGGER}$ threshold is crossed.	--	7	--	µs
ON_V_{IH}	ON Pin Input High Voltage		0.9	--	5	V
ON_V_{IL}	ON Pin Input Low Voltage		-0.3	0	0.3	V
$I_{ON(Leakage)}$	ON Pin Leakage Current	1 V ≤ ON ≤ 5 V or ON = GND	--	--	1	µA
$THERM_{ON}$	Thermal Protection Shutdown Threshold		--	125	--	°C
$THERM_{OFF}$	Thermal Protection Restart Threshold		--	100	--	°C

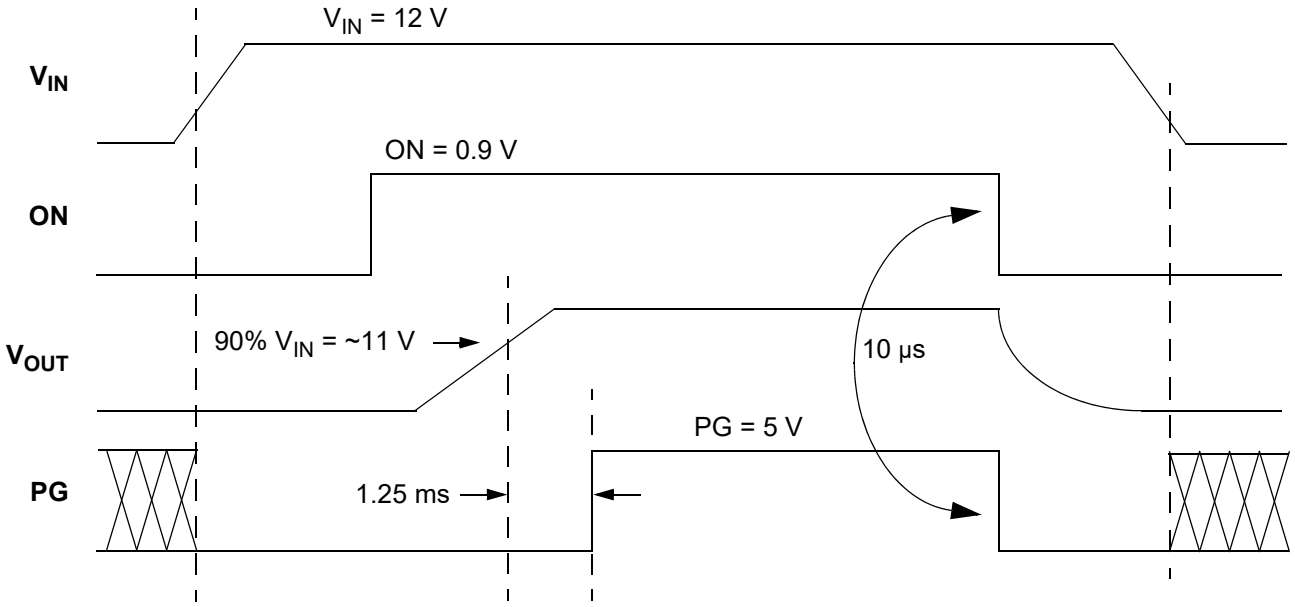
Notes:
1. Refer to typical Timing Parameter vs. C_{SLEW} performance charts for additional information when available.

T_{Total_ON}, T_{ON_Delay} and Slew Rate Measurement Timing Details



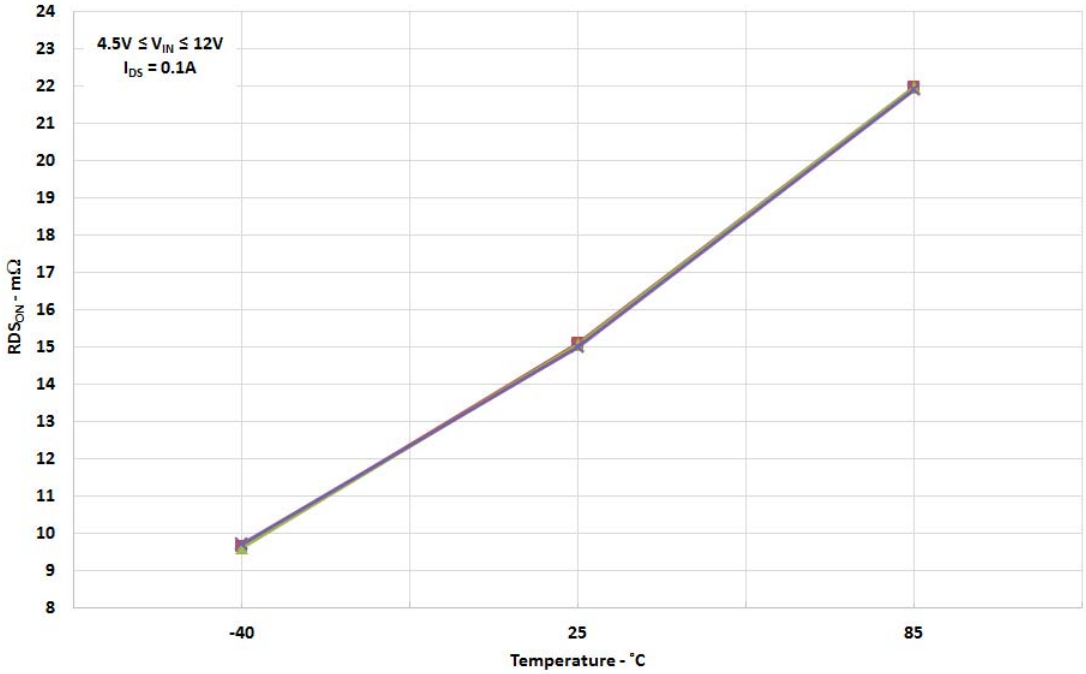
* Rise and Fall times of the ON signal are 100 ns

PG Timing Details

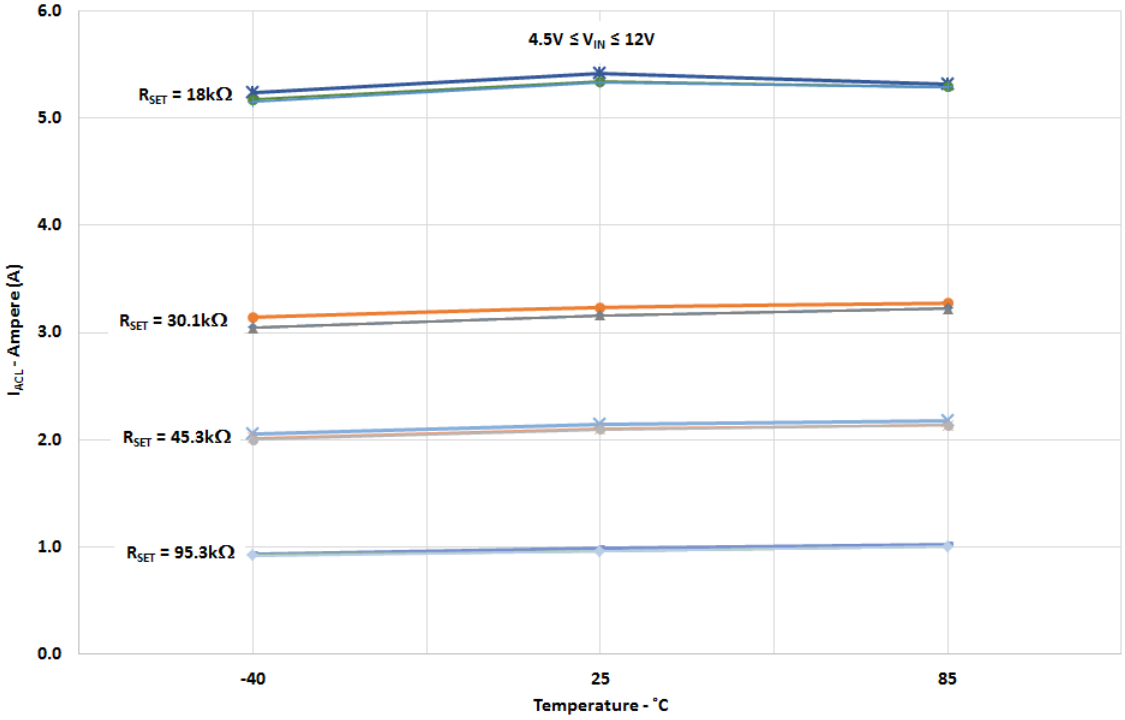


Typical Performance Characteristics

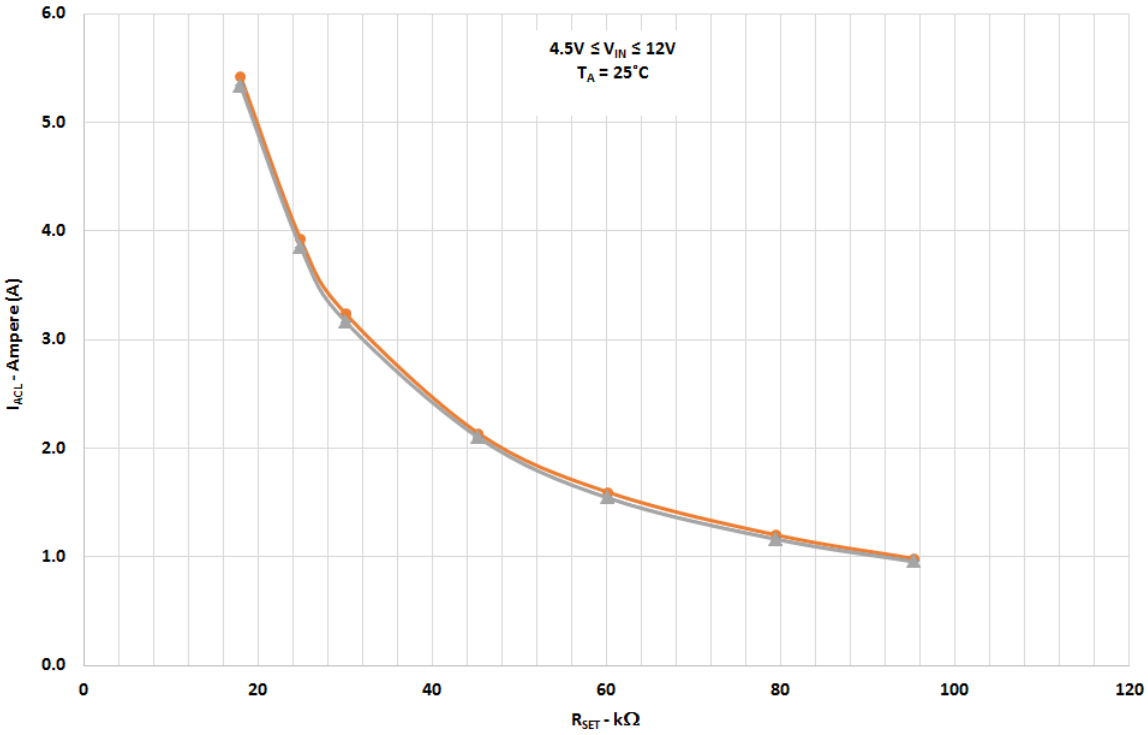
RDS_{ON} vs. Temperature and V_{IN}



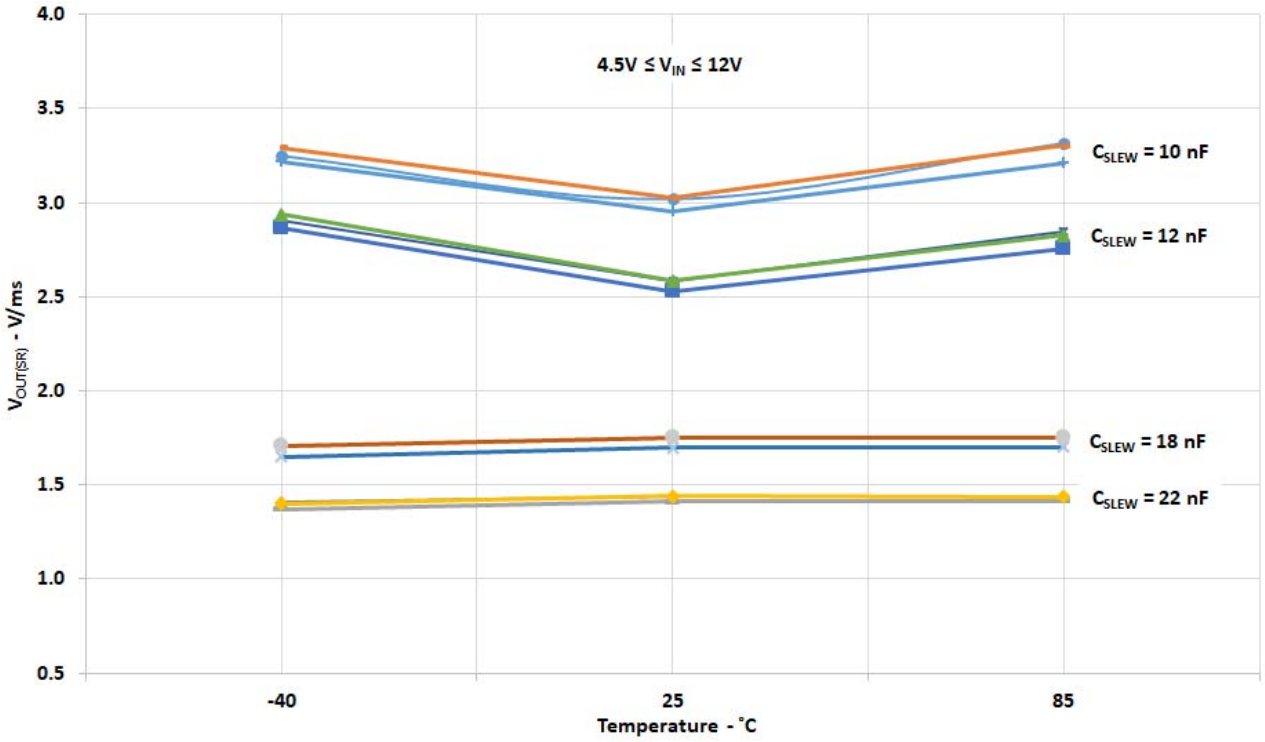
I_{ACL} vs. Temperature, R_{SET}, and V_{IN}



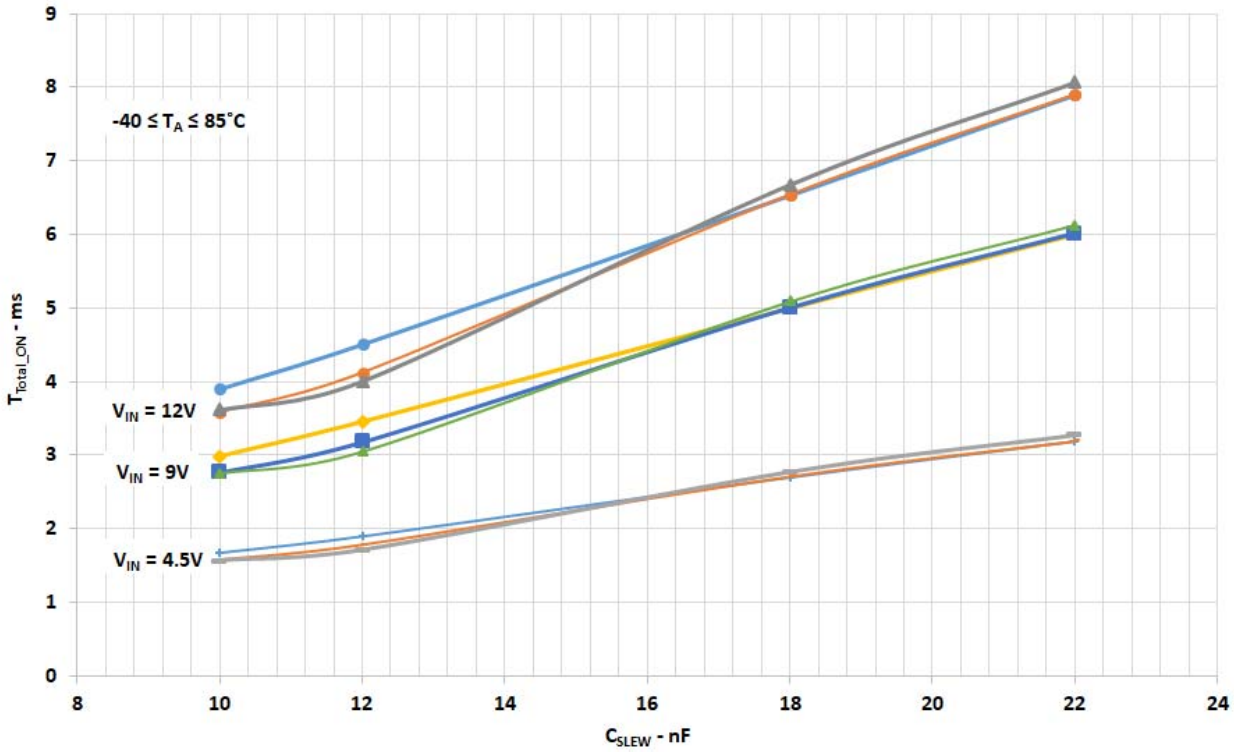
I_{ACL} vs. R_{SET}, and V_{IN}



V_{OUT} Slew Rate vs. Temperature, V_{IN}, and C_{SLEW}

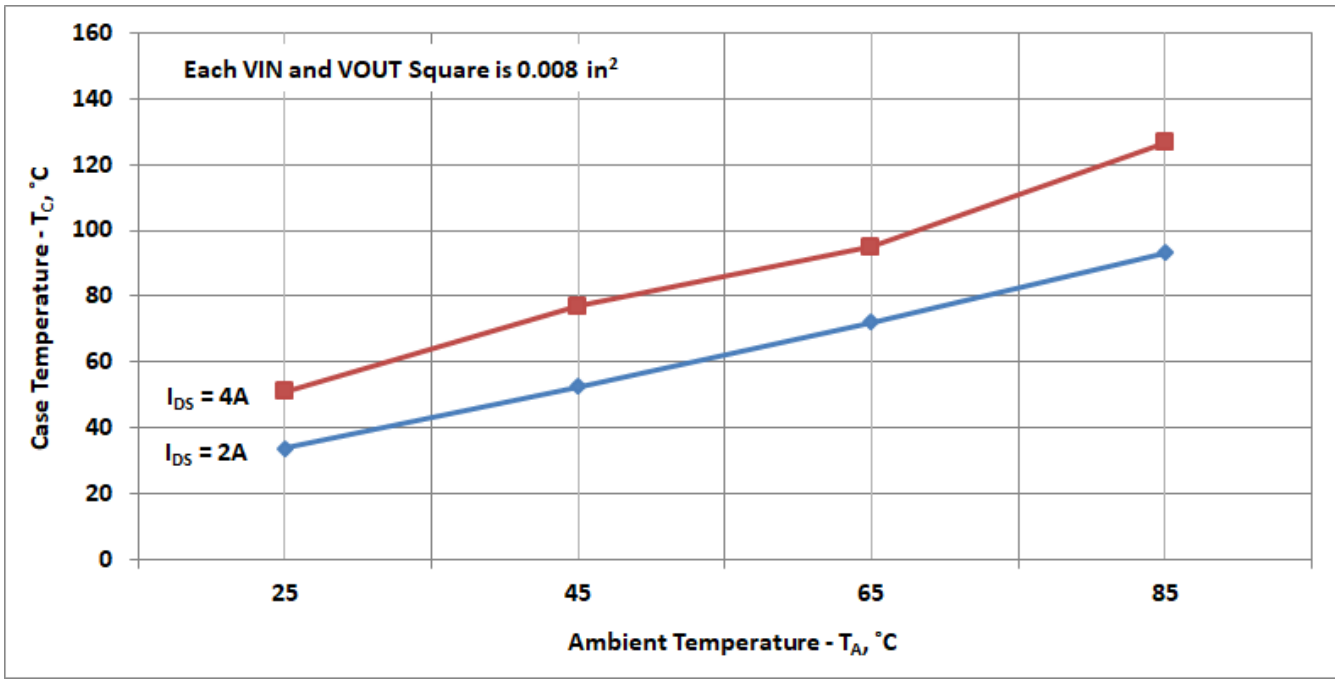


T_{Total_ON} vs. C_{SLEW}, V_{IN}, and Temperature

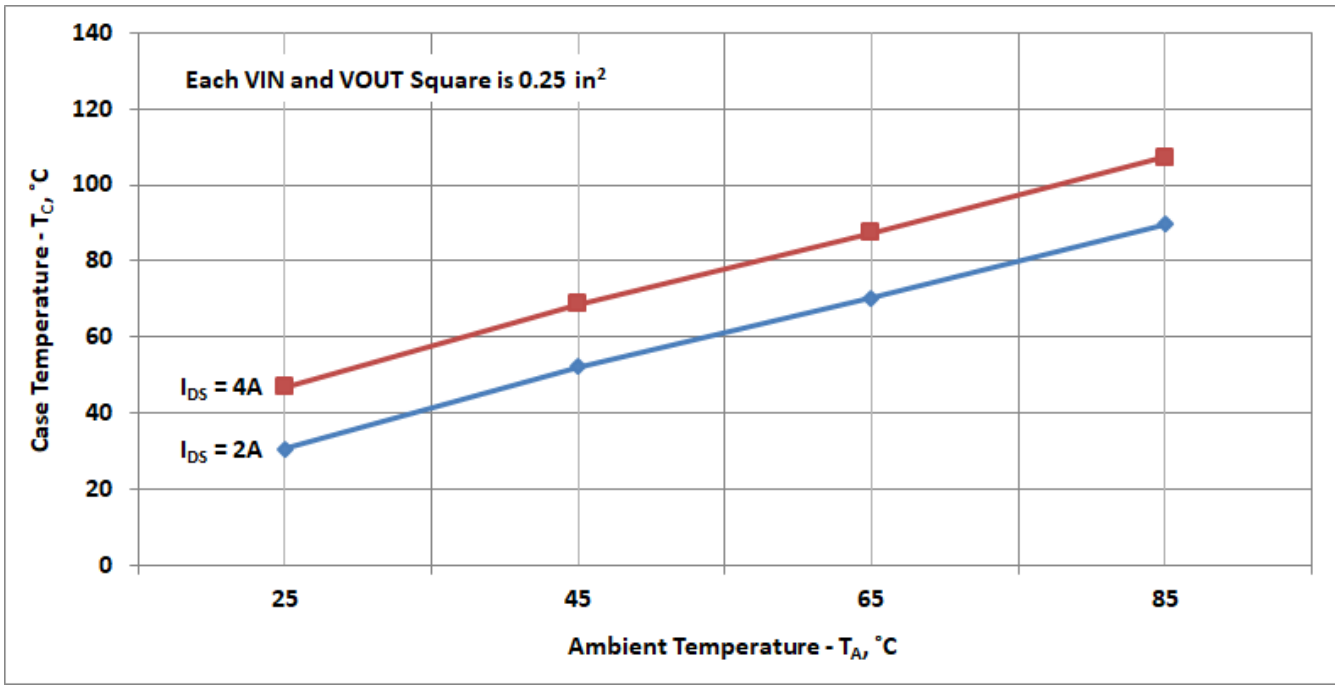


Case Measurement

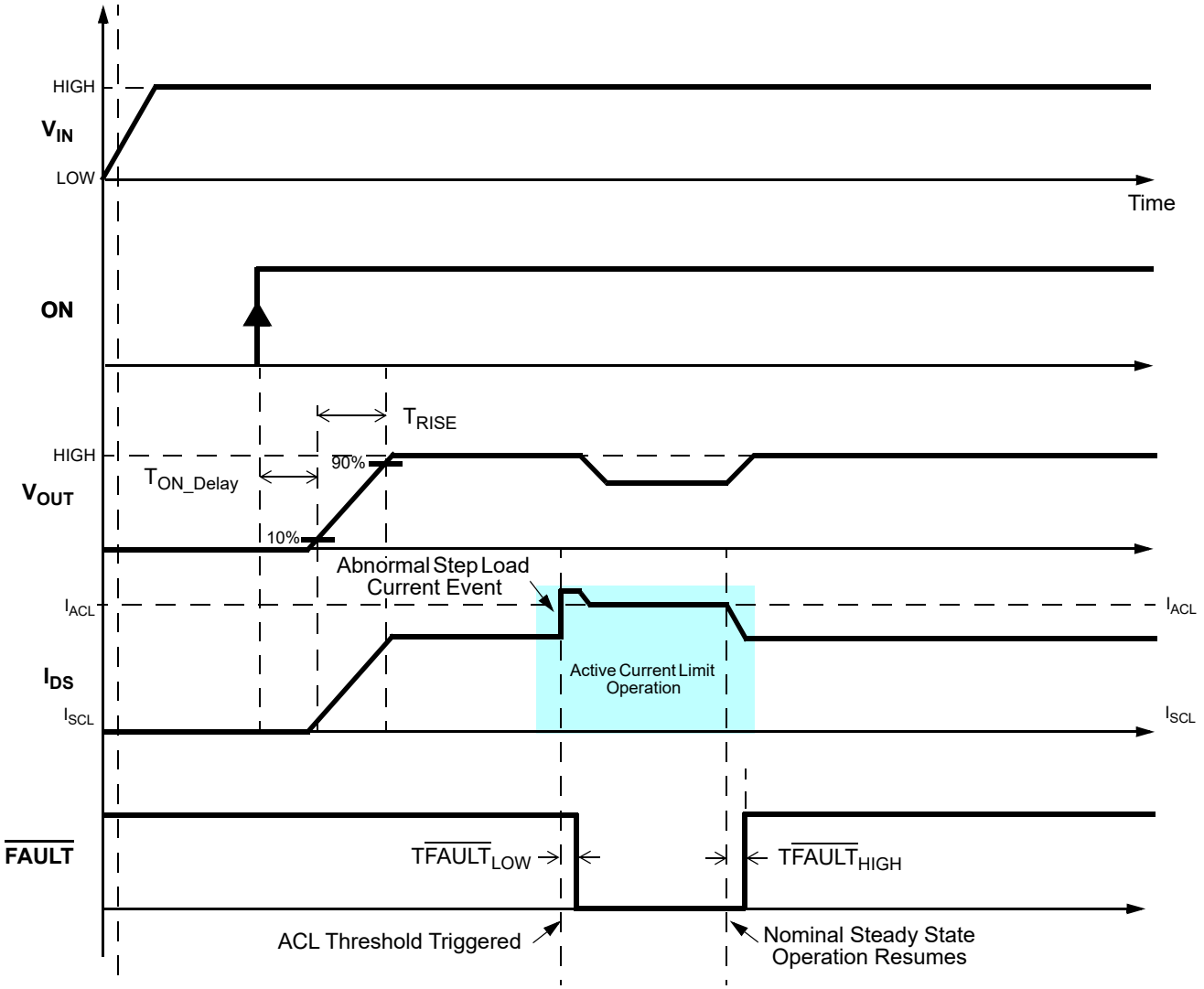
Case Temperature vs. Ambient Temperature (each VIN and VOUT square is 0.008 in^2, no airflow)



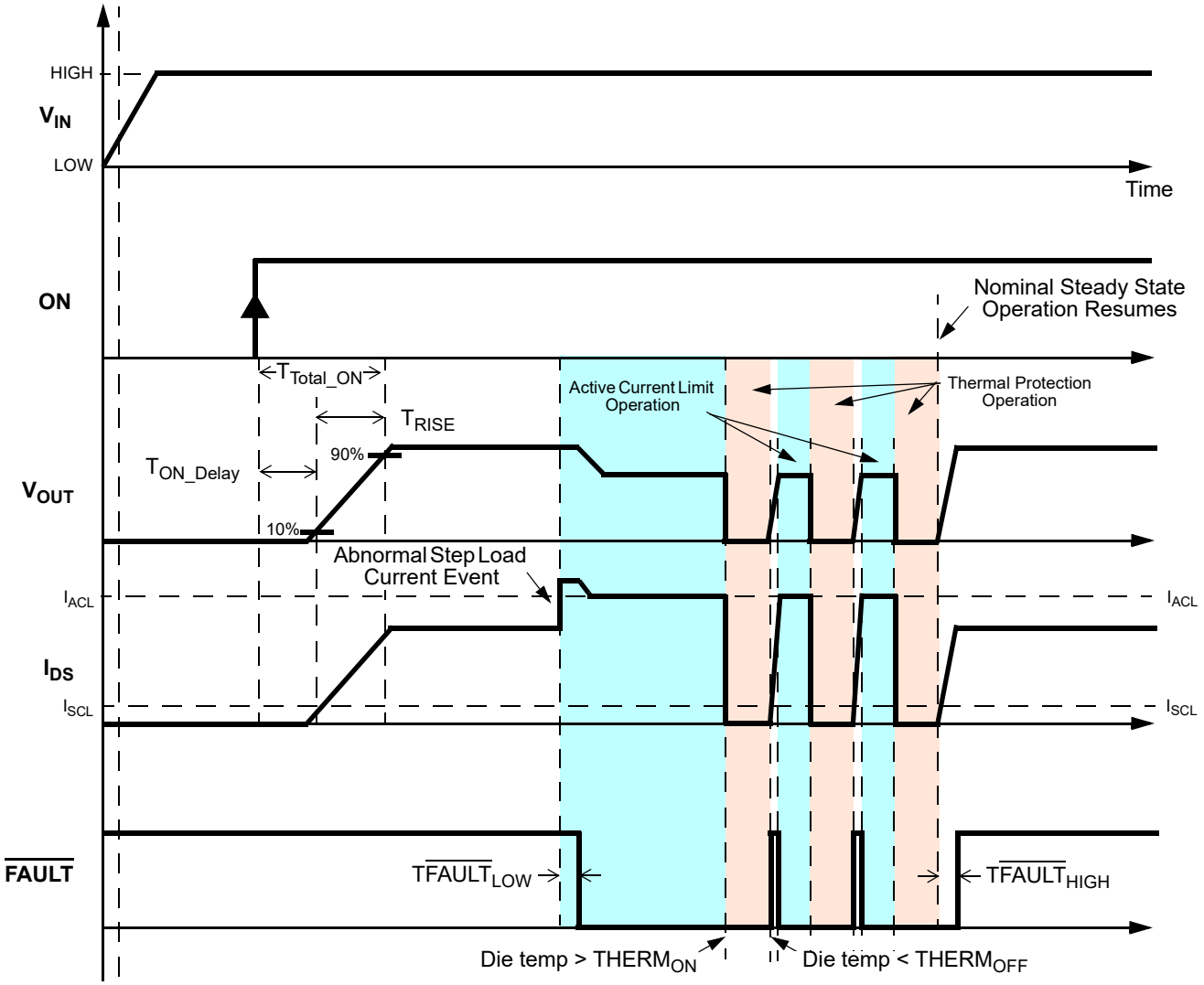
Case Temperature vs. Ambient Temperature (each VIN and VOUT square is 0.25 in^2, no airflow)



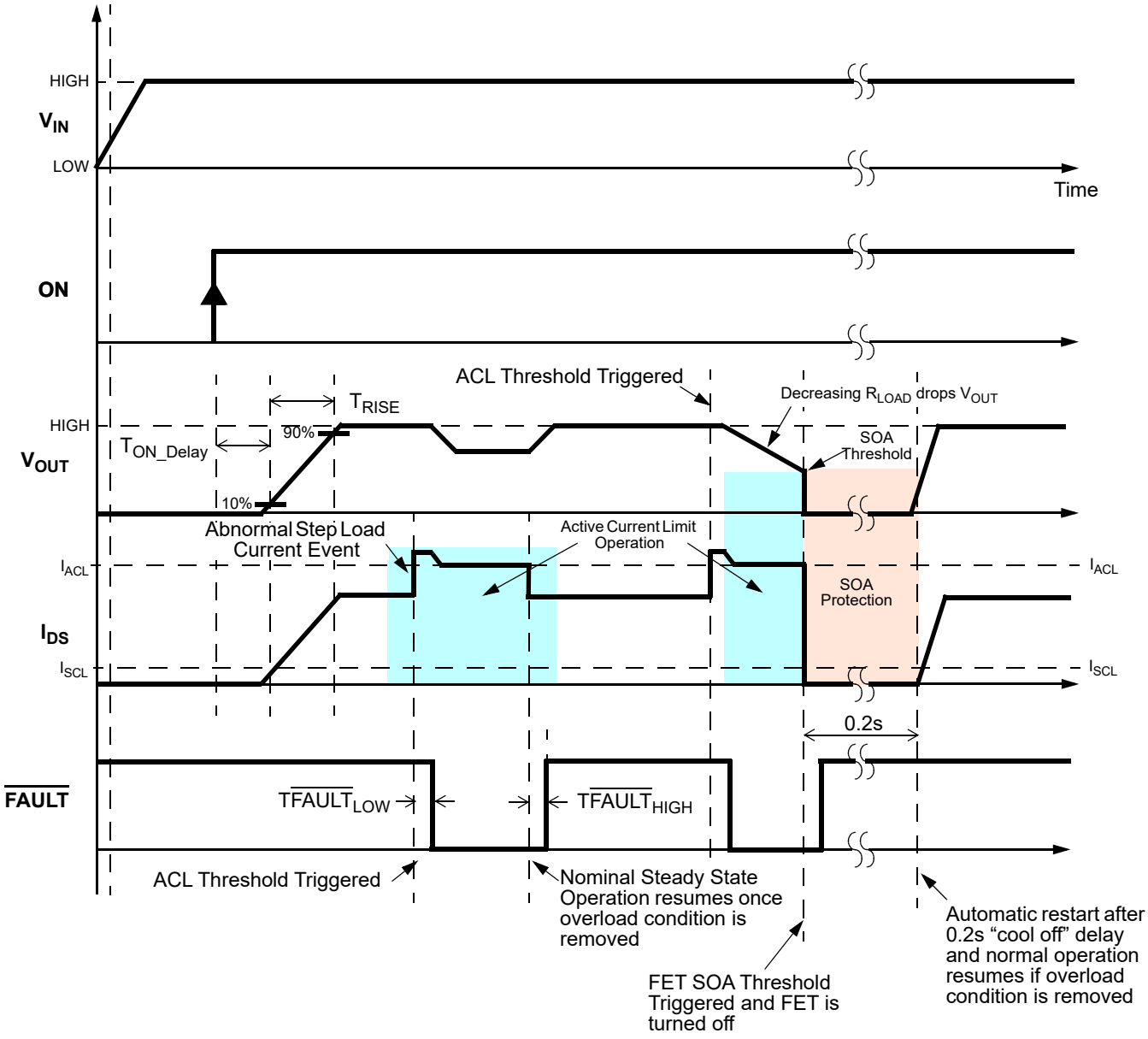
Timing Diagram - Basic Operation including Active Current Limit Protection



Timing Diagram - Active Current Limit & Thermal Protection Operation



Timing Diagram - Basic Operation including Active Current + Internal FET SOA Protection



SLG59H1127V Application Diagram

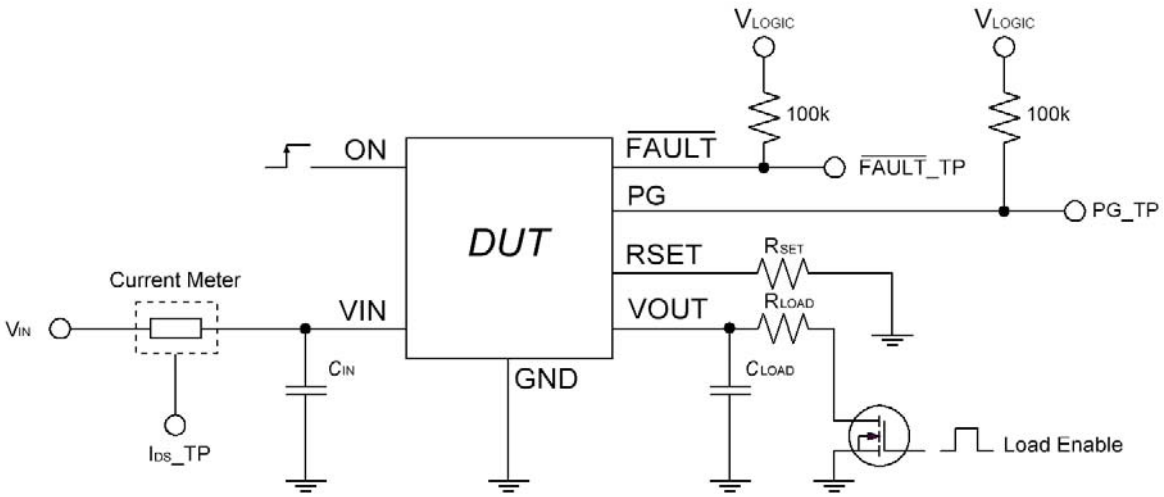


Figure 1. Test setup Application Diagram

Typical Turn-on Waveforms

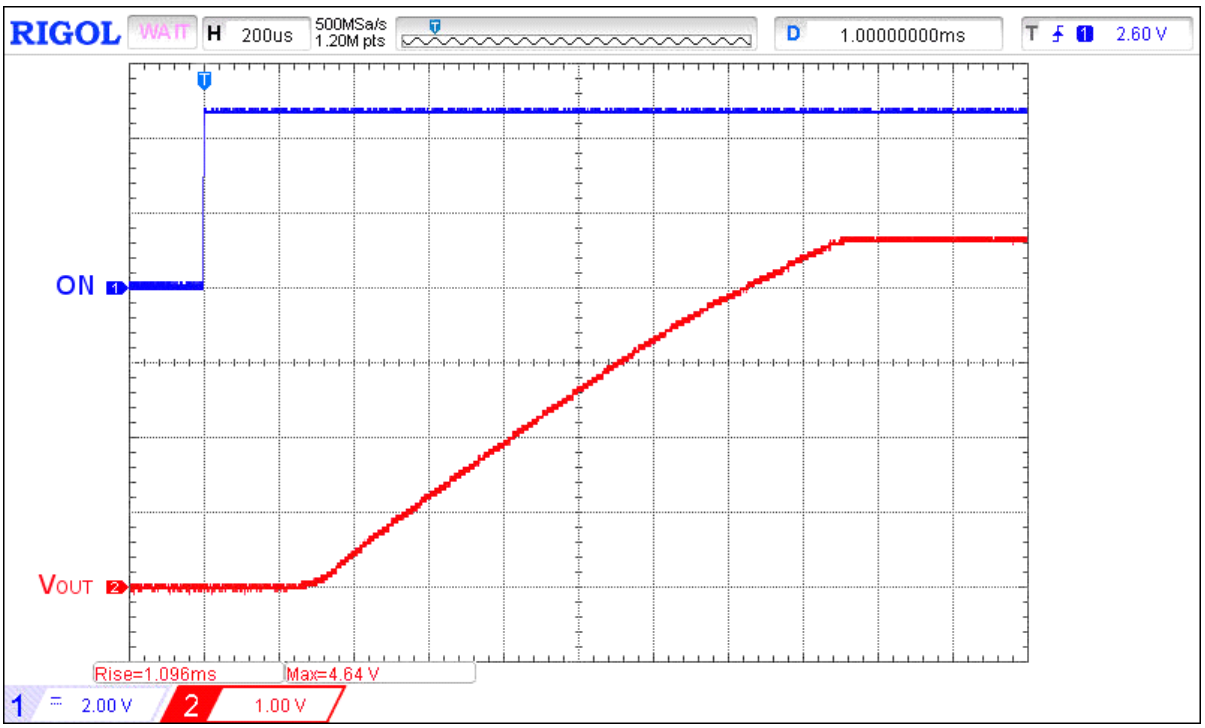


Figure 2. Typical Turn ON operation waveform for V_{IN} = 4.5 V, C_{SLEW} = 10 nF, C_{LOAD} = 10 µF, R_{LOAD} = 100 Ω

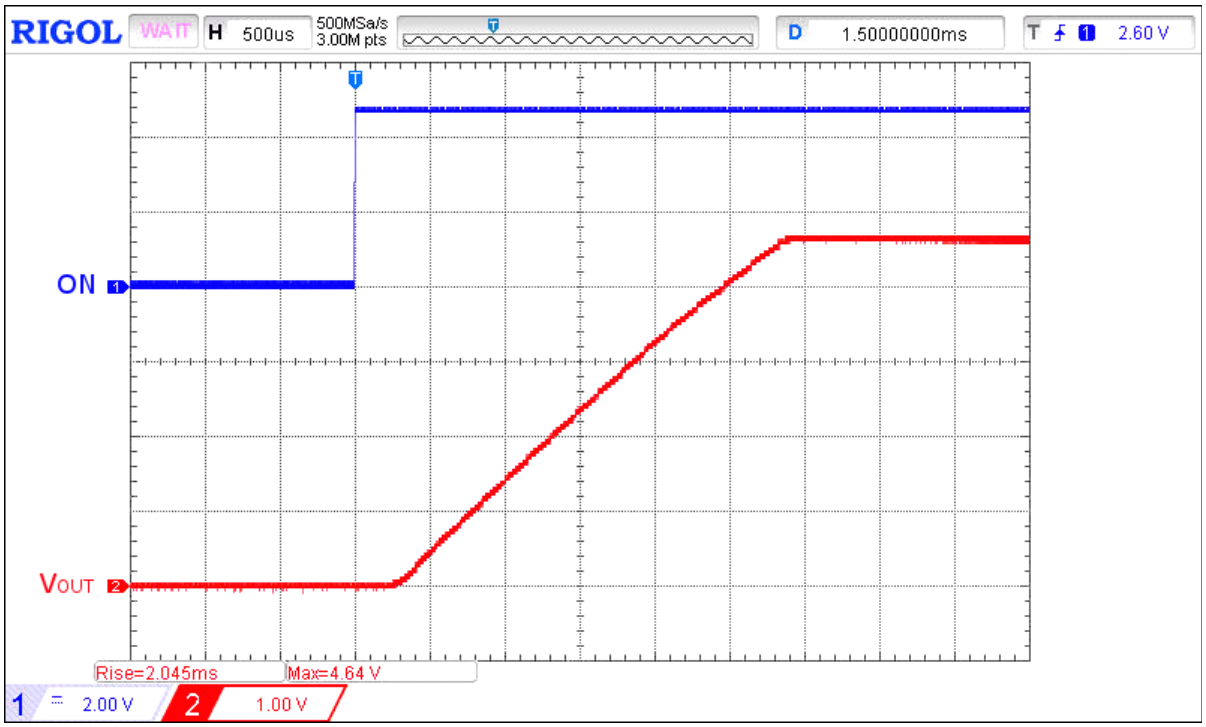


Figure 3. Typical Turn ON operation waveform for V_{IN} = 4.5 V, C_{SLEW} = 18 nF, C_{LOAD} = 10 µF, R_{LOAD} = 100 Ω

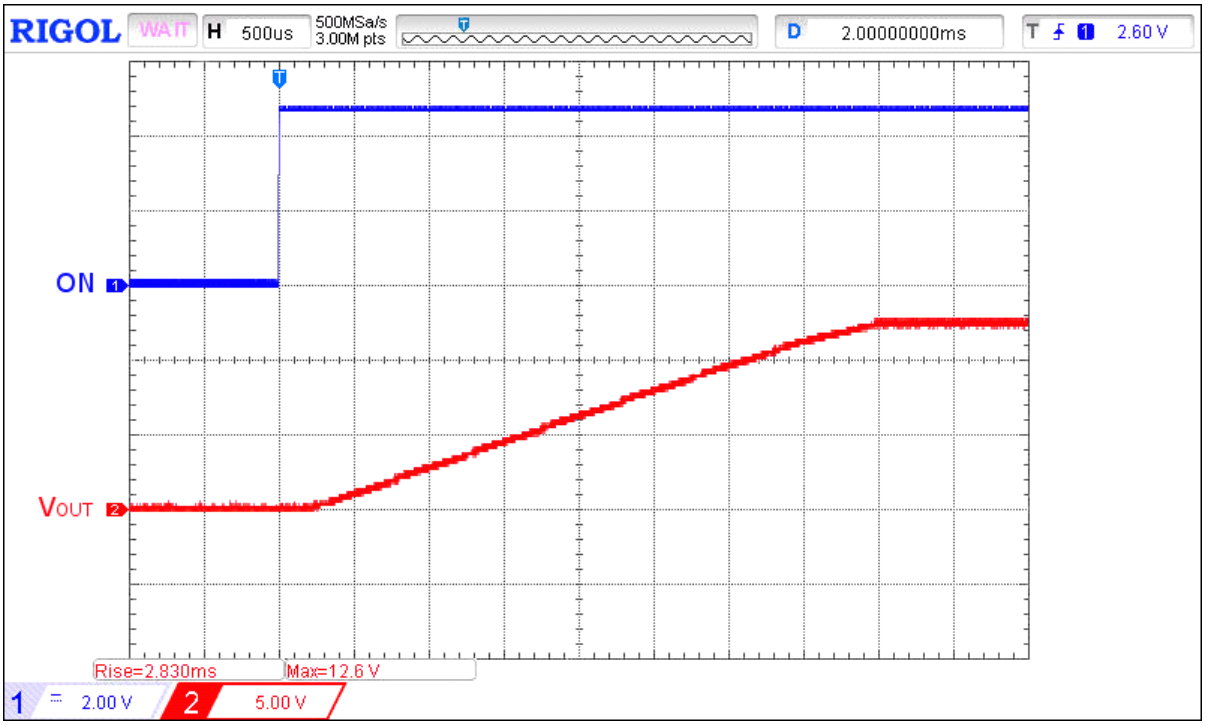


Figure 4. Typical Turn ON operation waveform for V_{IN} = 12 V, C_{SLEW} = 10 nF, C_{LOAD} = 10 µF, R_{LOAD} = 100 Ω

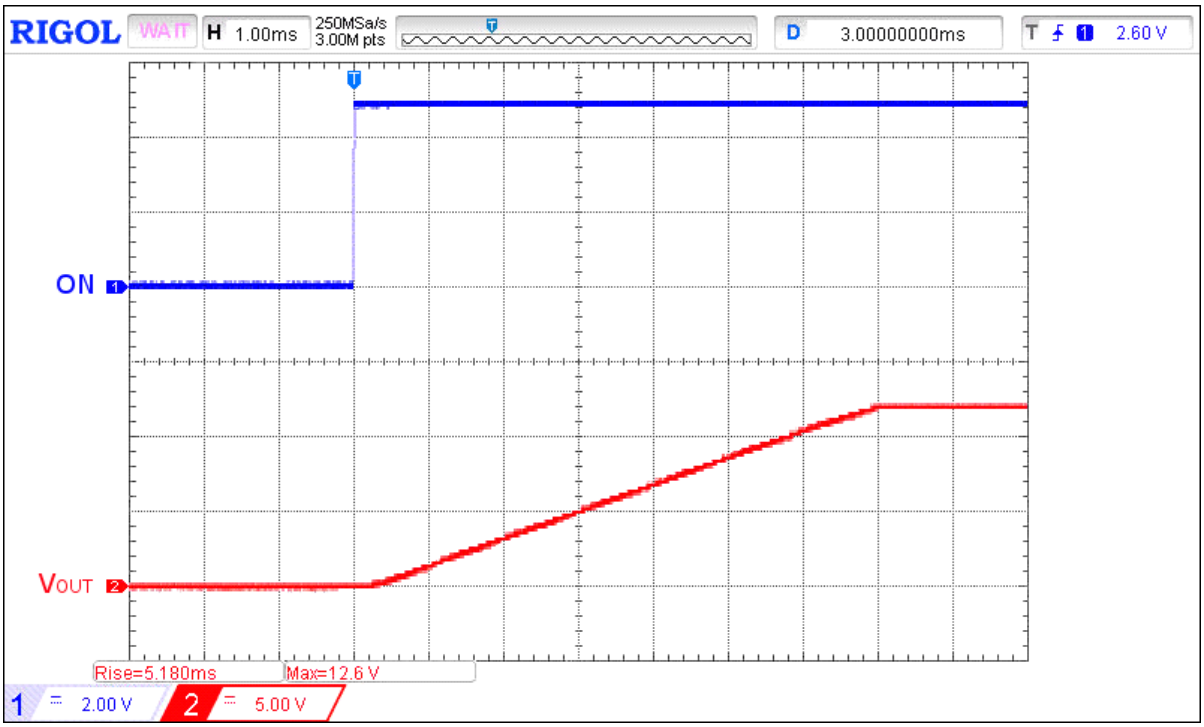


Figure 5. Typical Turn ON operation waveform for V_{IN} = 12 V, C_{SLEW} = 18 nF, C_{LOAD} = 10 µF, R_{LOAD} = 100 Ω

Typical Turn-off Waveforms

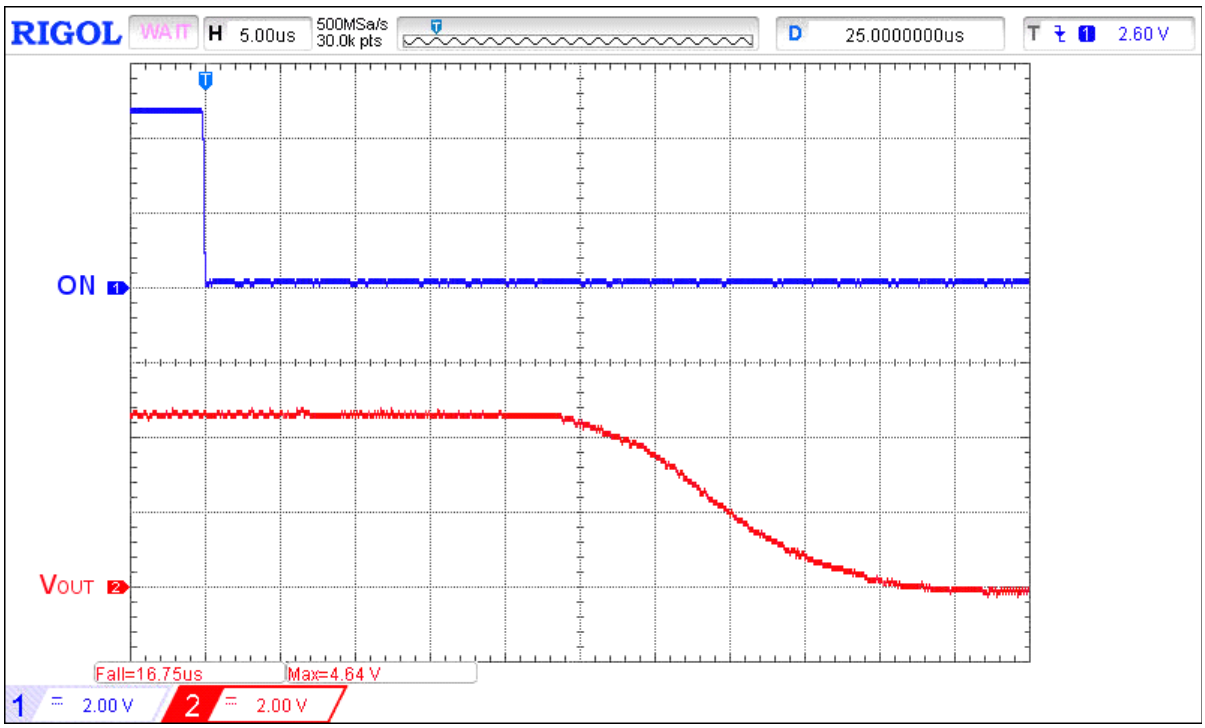


Figure 6. Typical Turn OFF operation waveform for V_{IN} = 4.5 V, C_{SLEW} = 10 nF, no C_{LOAD} , R_{LOAD} = 100 Ω

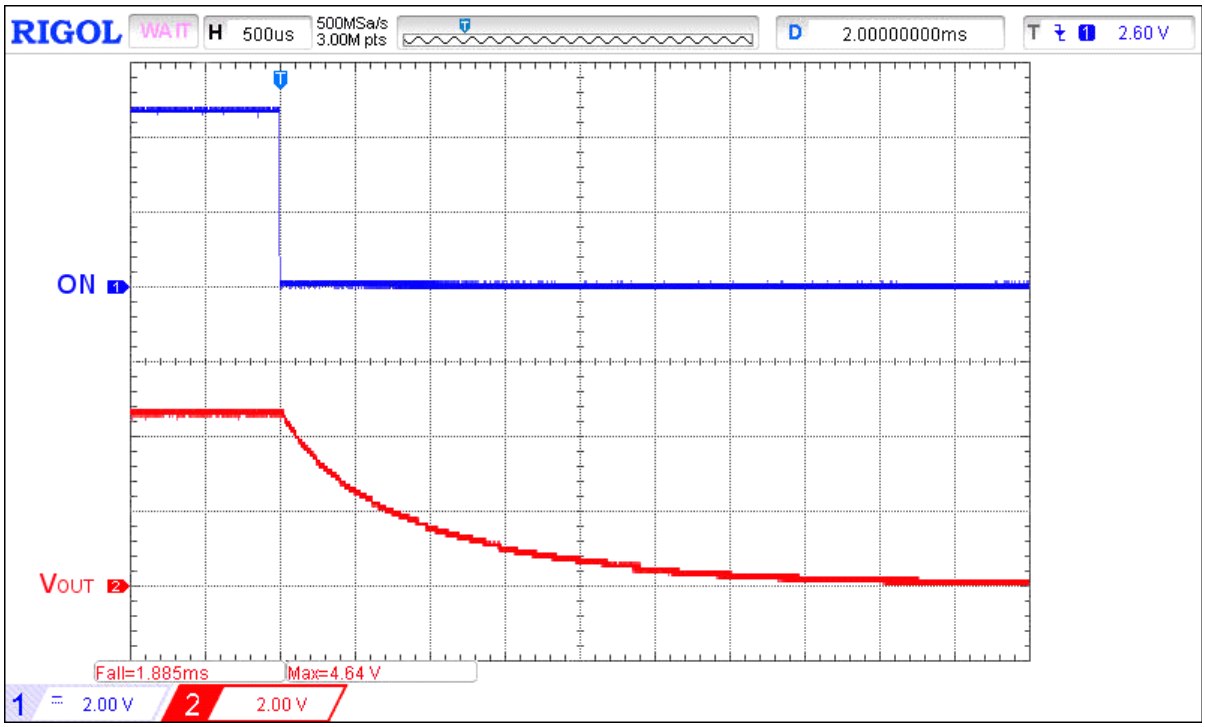


Figure 7. Typical Turn OFF operation waveform for V_{IN} = 4.5 V, C_{SLEW} = 10 nF, C_{LOAD} = 10 µF, R_{LOAD} = 100 Ω

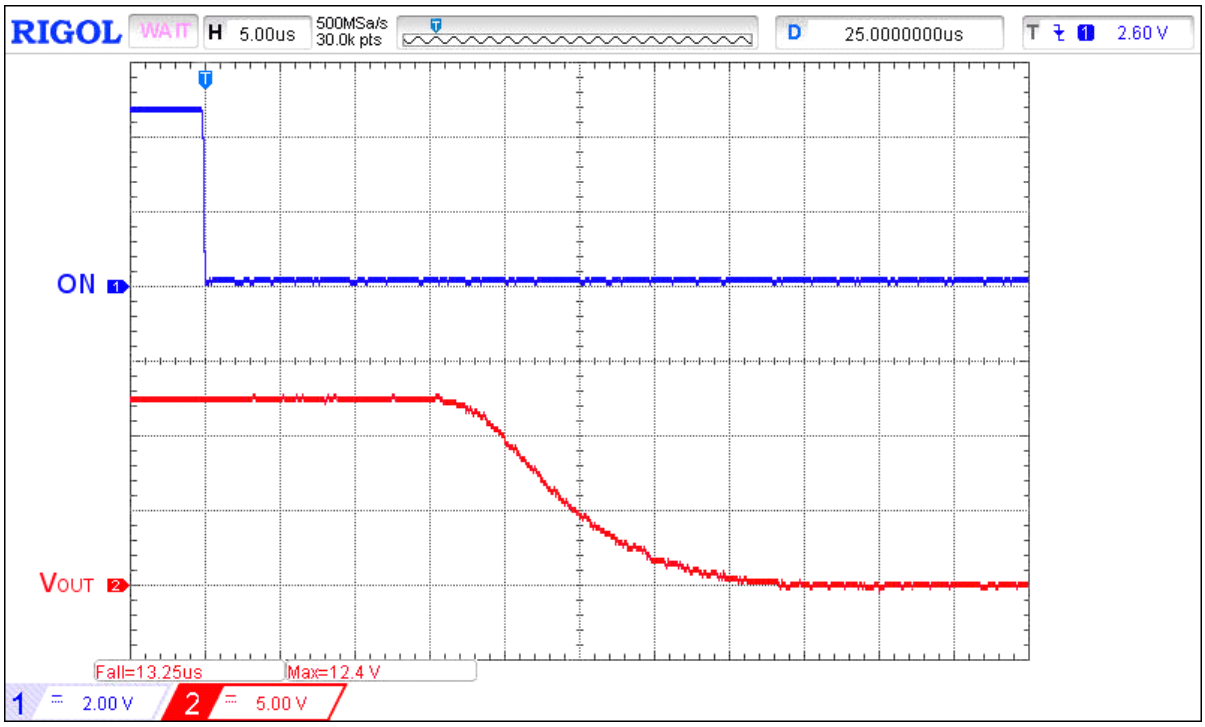


Figure 8. Typical Turn OFF operation waveform for V_{IN} = 12 V, C_{SLEW} = 10 nF, no C_{LOAD} , R_{LOAD} = 100 Ω

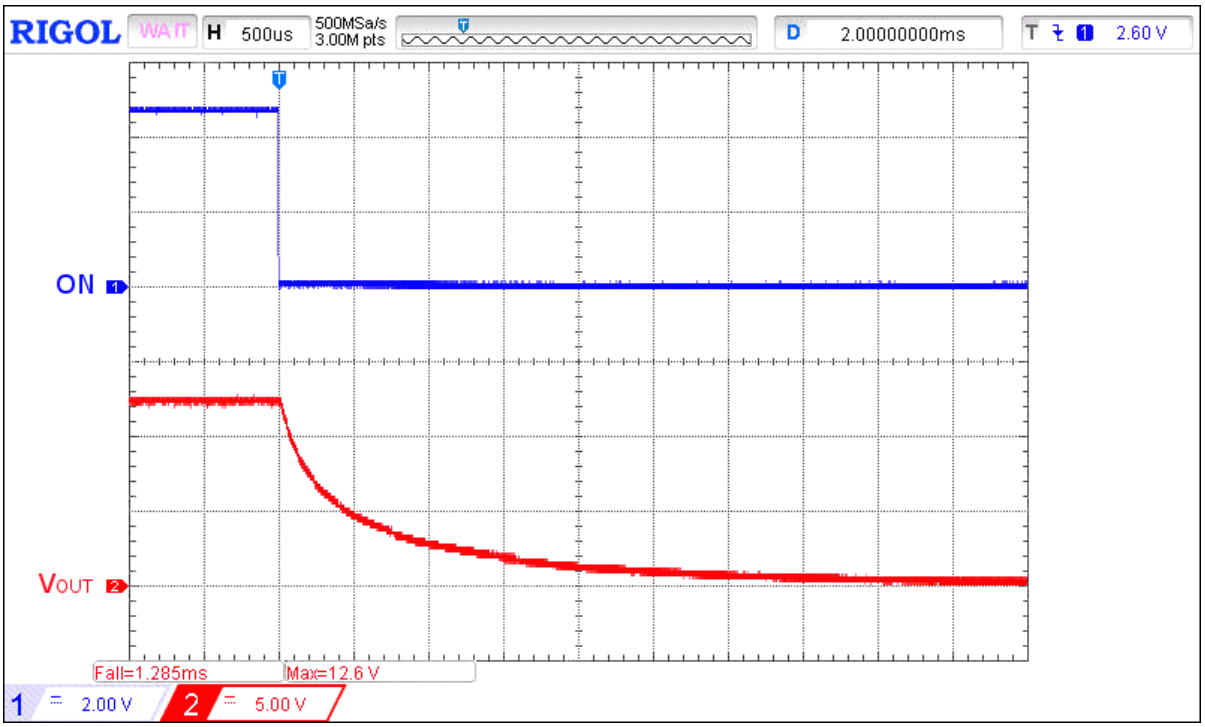


Figure 9. Typical Turn OFF operation waveform for V_{IN} = 12 V, C_{SLEW} = 10 nF, C_{LOAD} = 10 µF, R_{LOAD} = 100 Ω

Typical ACL Operation Waveforms

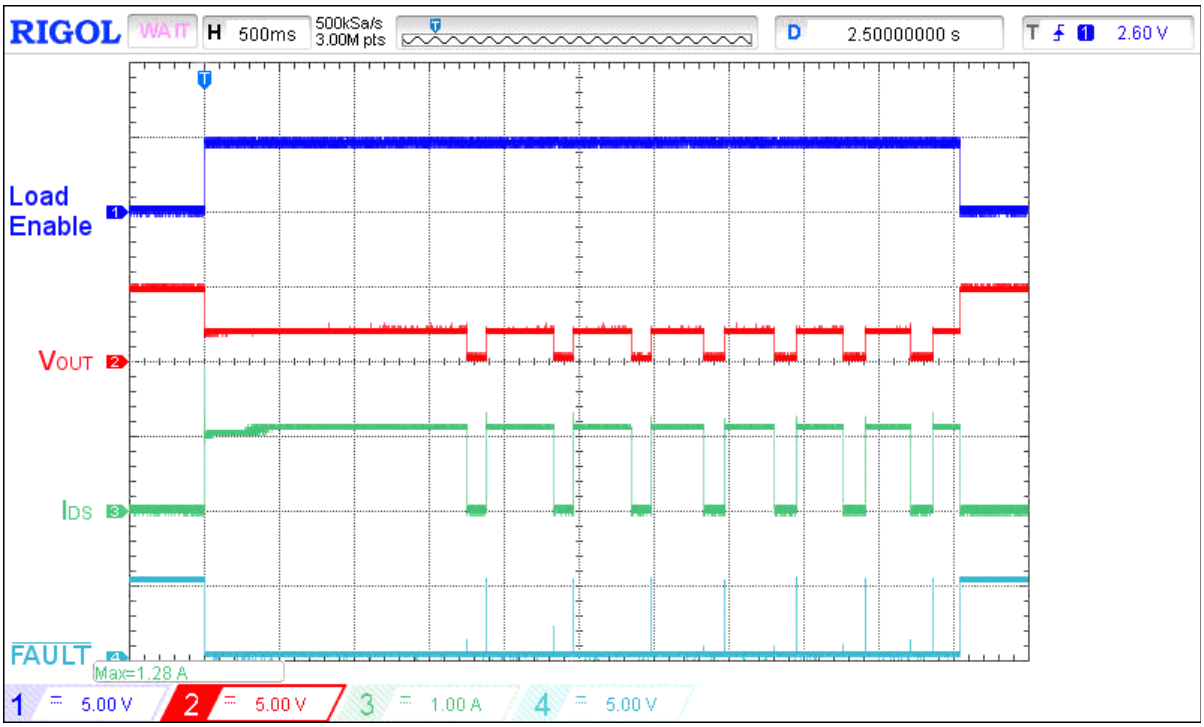


Figure 10. Typical ACL operation waveform for V_{IN} = 4.5 V, C_{LOAD} = 10 µF, I_{ACL} = 1 A, R_{SET} = 95.3 kΩ

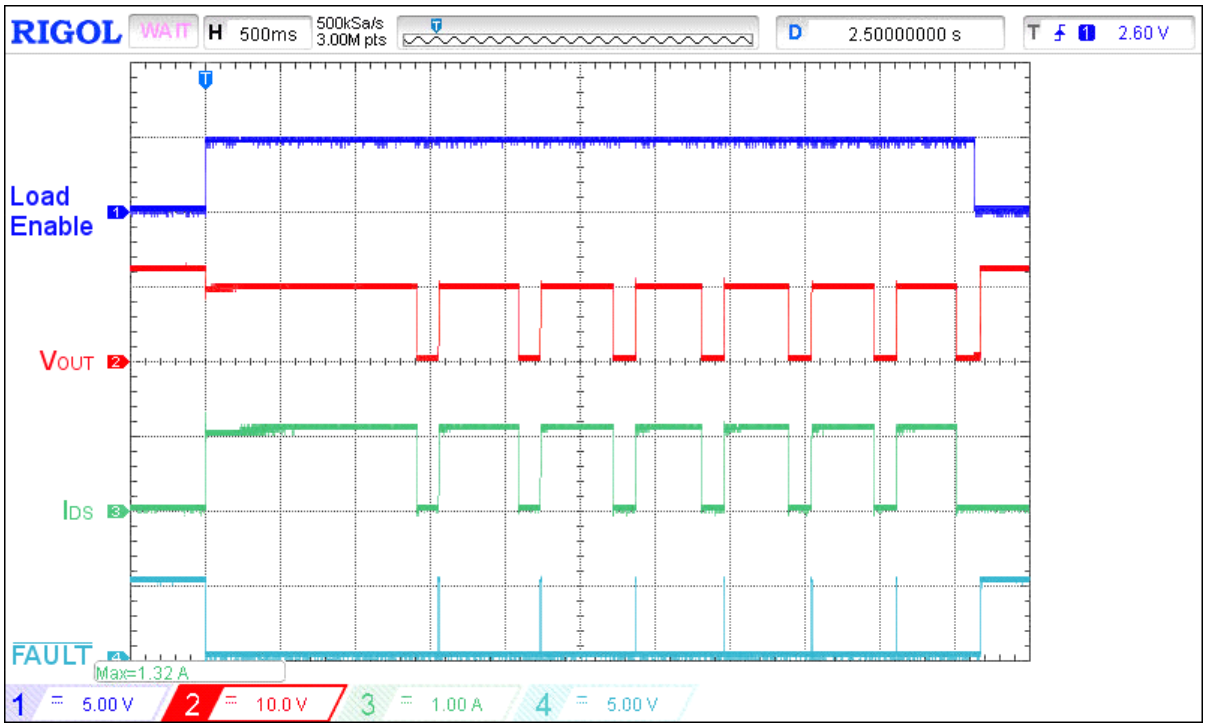


Figure 11. Typical ACL operation waveform for V_{IN} = 12 V, C_{LOAD} = 10 µF, I_{ACL} = 1 A, R_{SET} = 95.3 kΩ

Typical $\overline{\text{FAULT}}$ Operation Waveforms

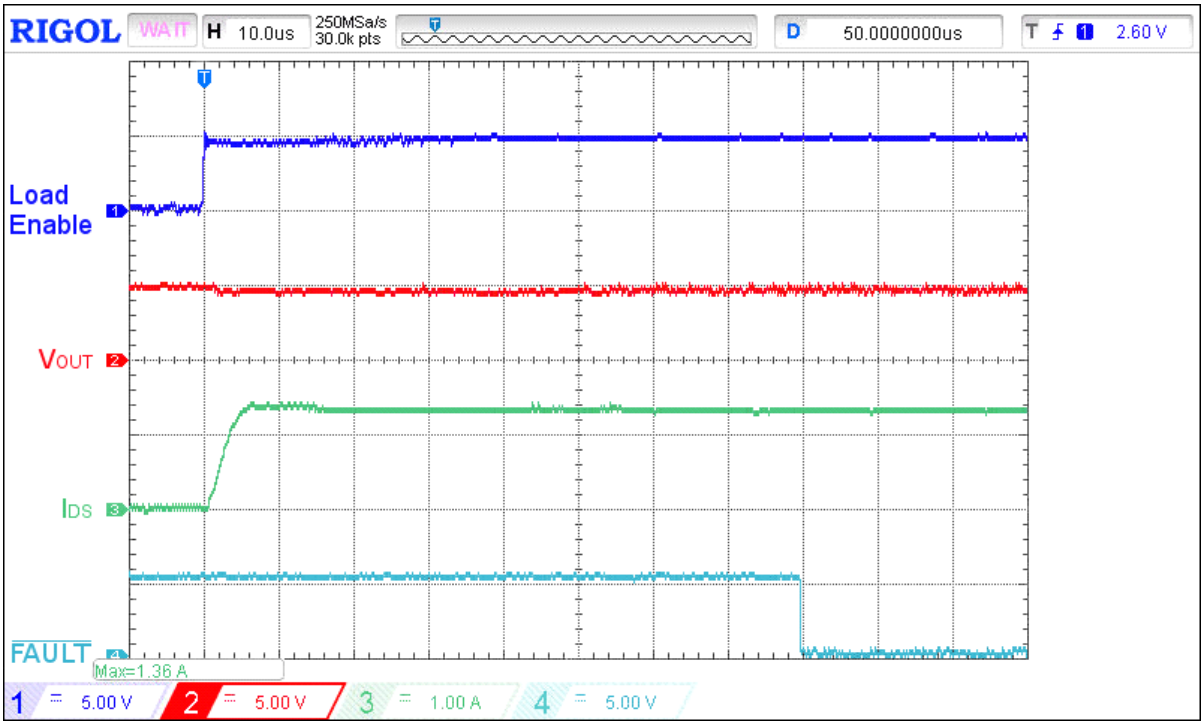


Figure 12. Typical $\overline{\text{FAULT}}$ assertion waveform for V_{IN} = 4.5 V, C_{LOAD} = 10 µF, I_{ACL} = 1 A, R_{SET} = 95.3 kΩ, switch on 3.3 Ω load

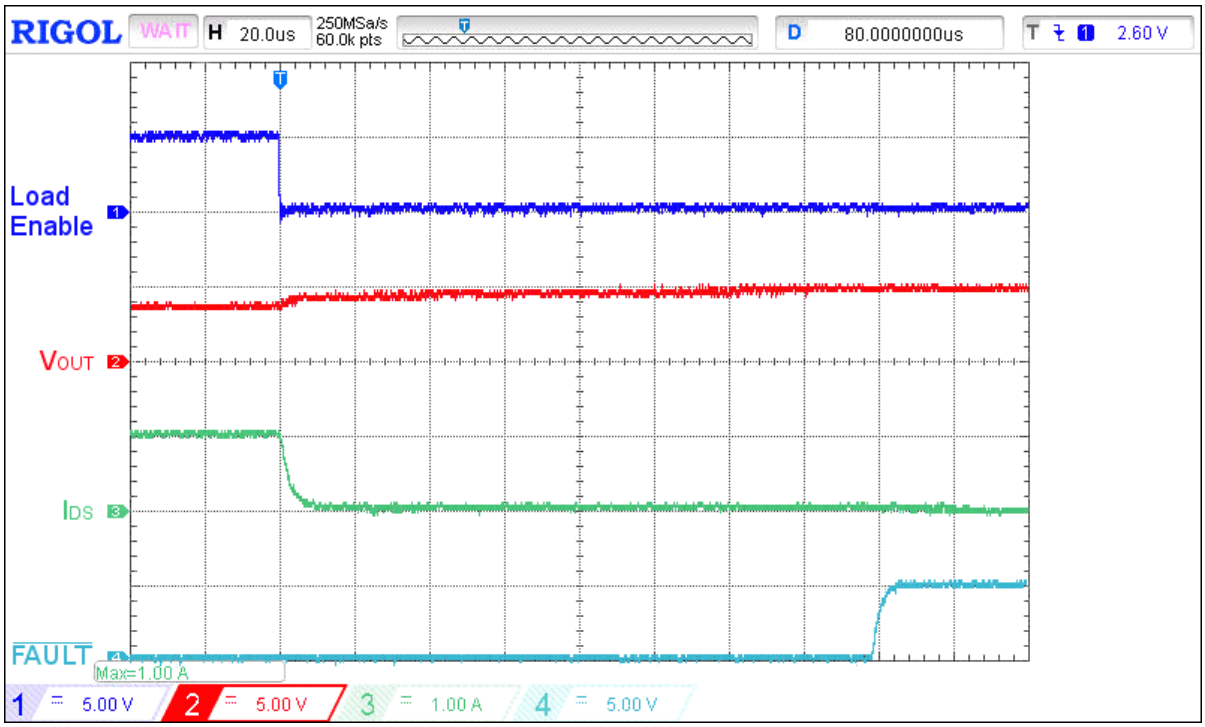


Figure 13. Typical $\overline{\text{FAULT}}$ de-assertion waveform for V_{IN} = 4.5 V, C_{LOAD} = 10 µF, I_{ACL} = 1 A, R_{SET} = 95.3 kΩ, switch out 3.3 Ω load

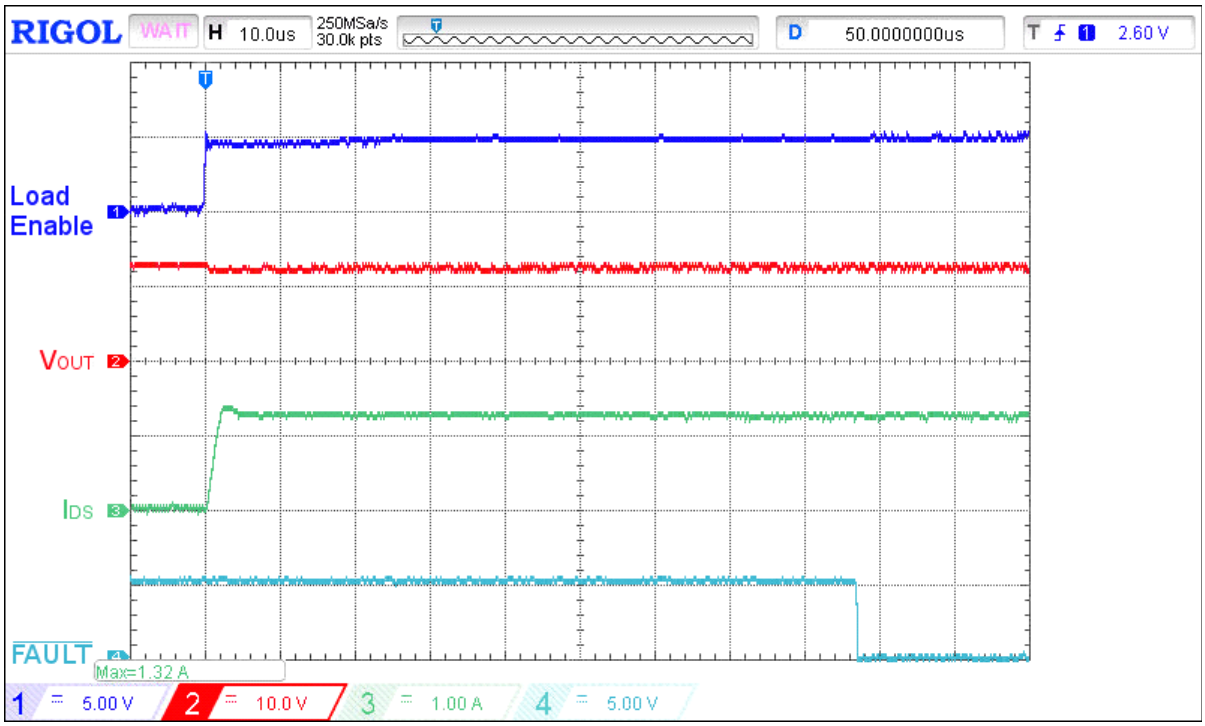


Figure 14. Typical $\overline{\text{FAULT}}$ assertion waveform for V_{IN} = 12 V, C_{LOAD} = 10 µF, I_{ACL} = 1 A, R_{SET} = 95.3 kΩ, switch on 10 Ω load

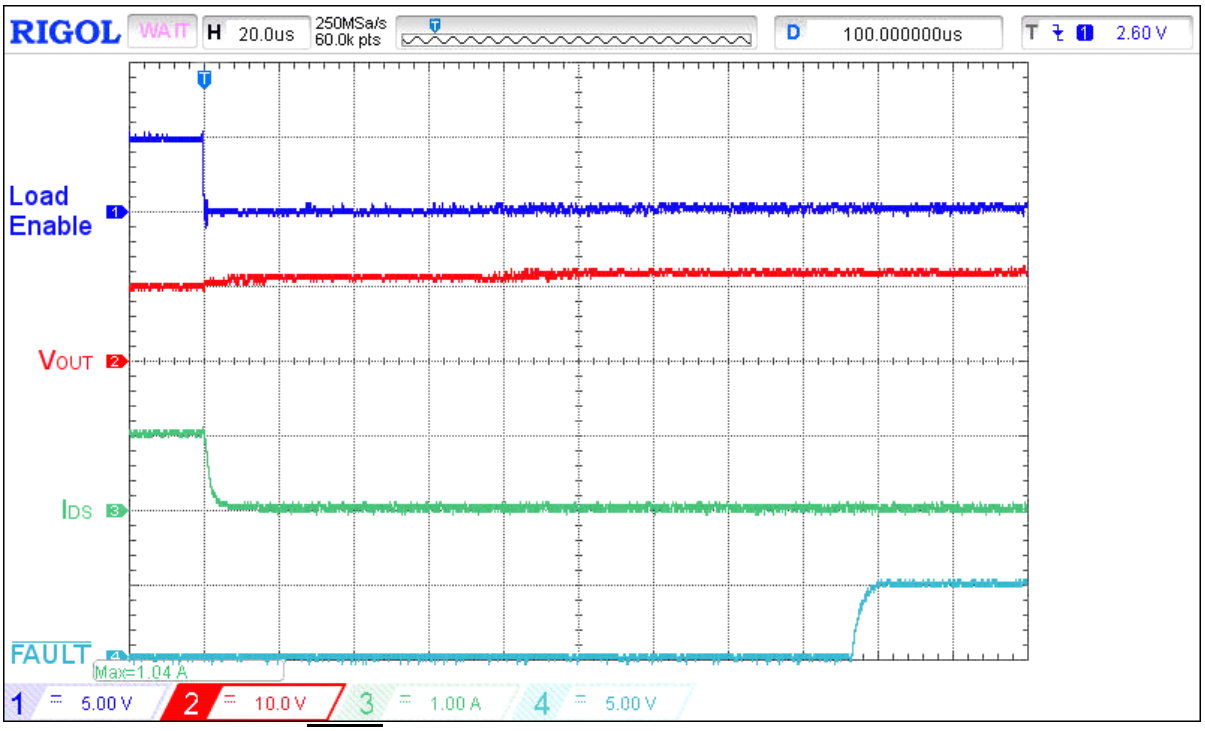


Figure 15. Typical $\overline{\text{FAULT}}$ de-assertion waveform for V_{IN} = 12 V, C_{LOAD} = 10 µF, I_{ACL} = 1 A, R_{SET} = 95.3 kΩ, switch out 10 Ω load

Typical Power Good Waveform

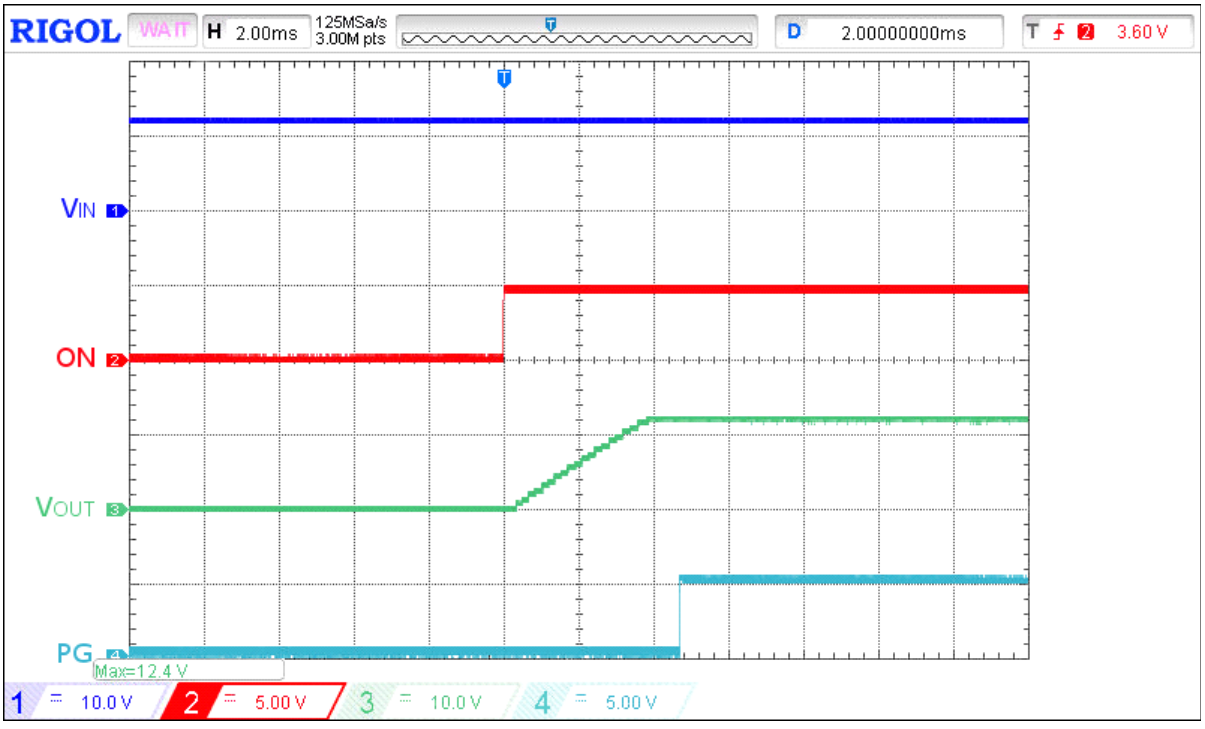


Figure 16. Typical Power Good operation waveform for V_{IN} = 12 V, C_{LOAD} = 10 µF, no R_{LOAD}

Typical SOA Waveforms

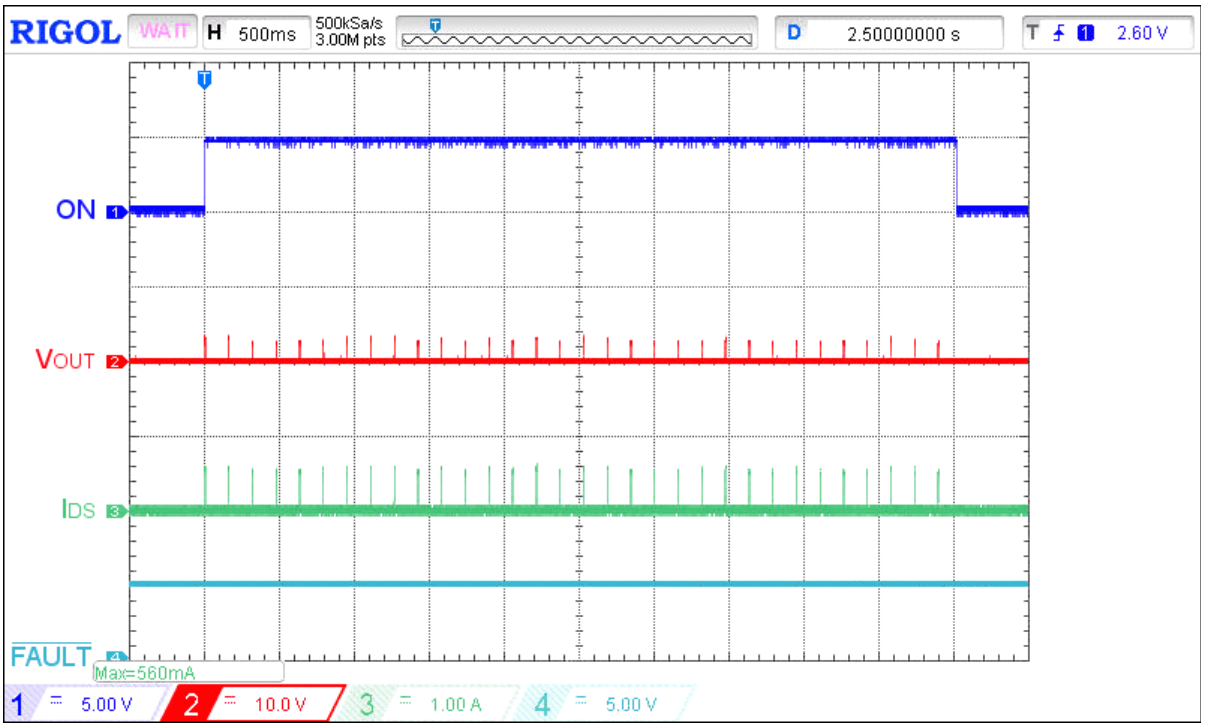


Figure 17. Typical SOA waveform during power up under heavy load for V_{IN} = 12 V, C_{LOAD} = 10 µF, R_{SET} = 30.1 kΩ, R_{LOAD} = 5 Ω

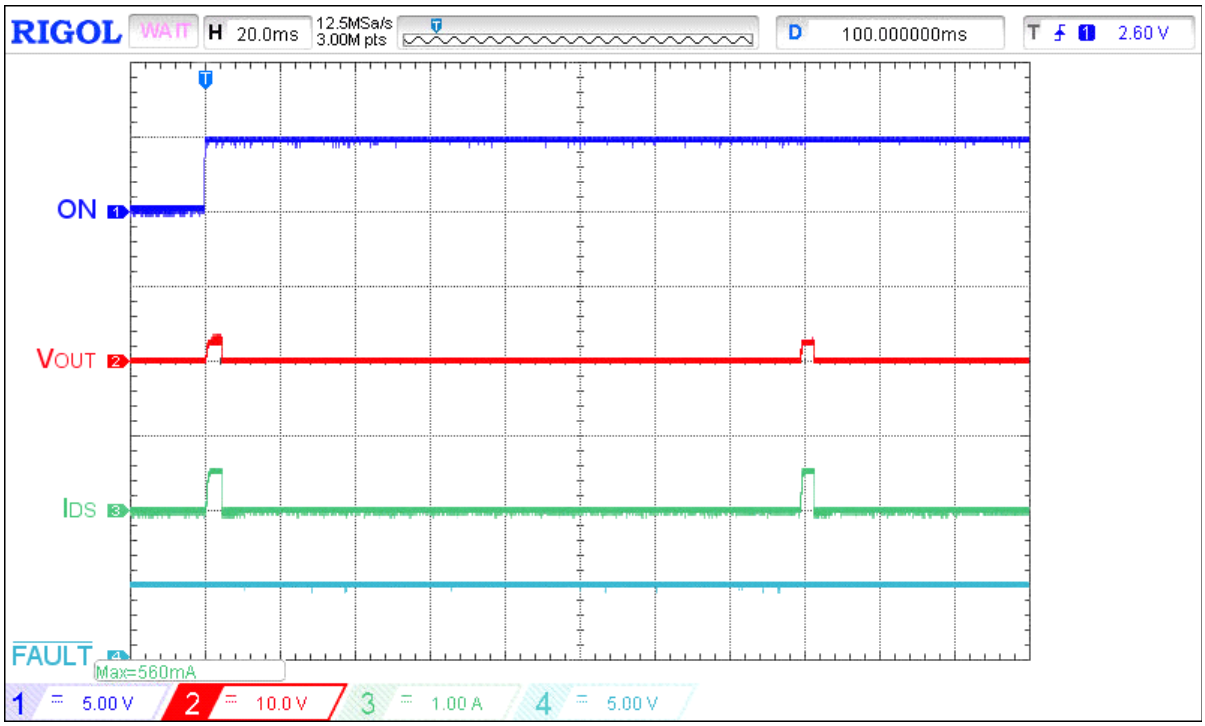


Figure 18. Extended typical SOA waveform during power up under heavy load for V_{IN} = 12 V, C_{LOAD} = 10 µF, R_{SET} = 30.1 kΩ, R_{LOAD} = 5 Ω

Applications Information

HFET1 Safe Operating Area Explained

Dialog's HFET1 integrated power controllers incorporate a number of internal protection features that prevents them from damaging themselves or any other circuit or subcircuit downstream of them. One particular protection feature is their Safe Operation Area (SOA) protection. SOA protection is automatically activated under overpower and, in some cases, under overcurrent conditions. Overpower SOA is activated if package power dissipation exceeds an internal 5W threshold longer than 2.5 ms. HFET1 devices will quickly switch off (open circuit) upon overpower detection and automatically resume (close) nominal operation once overpower condition no longer exists.

One of the possible ways to have an overpower condition trigger SOA protection is when HFET1 products are enabled into heavy output resistive loads and/or into large load capacitors. It is under these conditions to follow carefully the "Safe Start-up Loading" guidance in the Applications section of the datasheet. During an overcurrent condition, HFET1 devices will try to limit the output current to the level set by the external R_{SET} resistor. Limiting the output current, however, causes an increased voltage drop across the FET's channel because the FET's RDS_{ON} increased as well. Since the FET's RDS_{ON} is larger, package power dissipation also increases. If the resultant increase in package power dissipation is higher/equal than 5 W for longer than 2.5 ms, internal SOA protection will be triggered and the FET will open circuit (switch off). Every time SOA protection is triggered, all HFET1 devices will automatically attempt to resume nominal operation after 160 ms.

Safe Start-up Condition

SLG59H1127V has built-in protection to prevent over-heating during start-up into a heavy load. Overloading the VOUT pin with a capacitor and a resistor may result in non-monotonic V_{OUT} ramping or repeated restarts (*Figure 17* and *Figure 18*). In general, under light loading on VOUT, V_{OUT} ramping can be controlled with C_{SLEW} value. The following equation serves as a guide:

$$C_{SLEW} = \frac{T_{RISE}}{V_{IN}} \times 4.9\,\mu A \times \frac{20}{3}$$

where
T_{RISE} = Total rise time from 10% V_{OUT} to 90% V_{OUT}
V_{IN} = Input Voltage
C_{SLEW} = Capacitor value for CAP pin

When capacitor and resistor loading on VOUT during start up, the following tables will ensure V_{OUT} ramping is monotonic without triggering internal protection:

Safe Start-up Loading for V_{IN} = 12 V (Monotonic Ramp)			
Slew Rate (V/ms)	**C_{SLEW} (nF)[2]**	**C_{LOAD} (µF)**	**R_{LOAD} (Ω)**
1	33.3	500	20
2	16.7	250	20
3	11.1	160	20
4	8.3	120	20
5	6.7	100	20

Note 2: Select the closest-value tolerance capacitor.

Setting the SLG59H1127V's Active Current Limit

R_{SET} (kΩ)	Active Current Limit (A)[3]
91	1
45	2
30	3
18	5

Note 3: Active Current Limit accuracy is ±15% over voltage range and temperature range

Setting the SLG59H1127V's Input Overvoltage Lockout Threshold

As shown in the table below, SEL selects the V_{IN} overvoltage threshold at which the SLG59H1127V's internal state machine will turn OFF (open circuit) the power MOSFET if V_{IN} exceeds the selected threshold.

SEL	$V_{IN(OVLO)}$ (Typ)
0	14.4 V

With an activated SLG59H1127V (ON=HIGH) and at any time V_{IN} crosses the programmed V_{IN} overvoltage threshold, the state machine opens the power switch and asserts the $\overline{FAULT}$ pin within $TFAULT_{LOW}$.

In applications with a deactivated or inactive SLG59H1127V ($V_{IN} > V_{IN(UVLO)}$ and ON=LOW) and if the applied V_{IN} is higher than the programmed $V_{IN(OVLO)}$ threshold, the SLG59H1127V's state machine will keep the power switch open circuited if the ON pin is toggled LOW-to-HIGH. In these cases, the $\overline{FAULT}$ pin will also be asserted within $TFAULT_{LOW}$ and will remain asserted until V_{IN} resumes nominal, steady-state operation.

In all cases, the SLG59H1127V's V_{IN} undervoltage lockout threshold is fixed at $V_{IN(UVLO)}$.

Power Dissipation

The junction temperature of the SLG59H1127V depends on different factors such as board layout, ambient temperature, and other environmental factors. The primary contributor to the increase in the junction temperature of the SLG59H1127V is the power dissipation of its power MOSFET. Its power dissipation and the junction temperature in nominal operating mode can be calculated using the following equations:

$$PD = RDS_{ON} \times I_{DS}^2$$

where:

PD = Power dissipation, in Watts (W)
RDS_{ON} = Power MOSFET ON resistance, in Ohms (Ω)
I_{DS} = MOSFET current, in Amps (A)

and

$$T_J = PD \times \theta_{JA} + T_A$$

where:

T_J = Junction temperature, in Celsius degrees (°C)
θ_{JA} = Package thermal resistance, in Celsius degrees per Watt (°C/W)
T_A = Ambient temperature, in Celsius degrees (°C)

Power Dissipation (continued)

In current-limit mode, the SLG59H1127V's power dissipation can be calculated by taking into account the voltage drop across the power switch (V_{IN} - V_{OUT}) and the magnitude of the output current in current-limit mode (I_{ACL}):

$$PD = (V_{IN}-V_{OUT}) \times I_{ACL} \text{ or}$$

$$PD = (V_{IN} – (R_{LOAD} \times I_{ACL})) \times I_{ACL}$$

where:

PD = Power dissipation, in Watts (W)
V_{IN} = Input Voltage, in Volts (V)
R_{LOAD} = Load Resistance, in Ohms (Ω)
I_{ACL} = Output limited current, in Amps (A)
$V_{OUT} = R_{LOAD} \times I_{ACL}$

Layout Guidelines:

1. Since the VIN and VOUT pins dissipate most of the heat generated during high-load current operation, it is highly recommended to make power traces as short, direct, and wide as possible. A good practice is to make power traces with absolute minimum widths of 15 mils (0.381 mm) per Ampere. A representative layout, shown in Figure 19, illustrates proper techniques for heat to transfer as efficiently as possible out of the device;

2. To minimize the effects of parasitic trace inductance on normal operation, it is recommended to connect input C_{IN} and output C_{LOAD} low-ESR capacitors as close as possible to the SLG59H1127V's VIN and VOUT pins;

3. The GND pin should be connected to system analog or power ground plane.

4. 2 oz. copper is recommended for high current operation.

SLG59H1127V Evaluation Board:

A HFET1 Evaluation Board for SLG59H1127V is designed according to the statements above and is illustrated on Figure 19. Please note that evaluation board has D_Sense and S_Sense pads. They cannot carry high currents and dedicated only for RDS_{ON} evaluation.

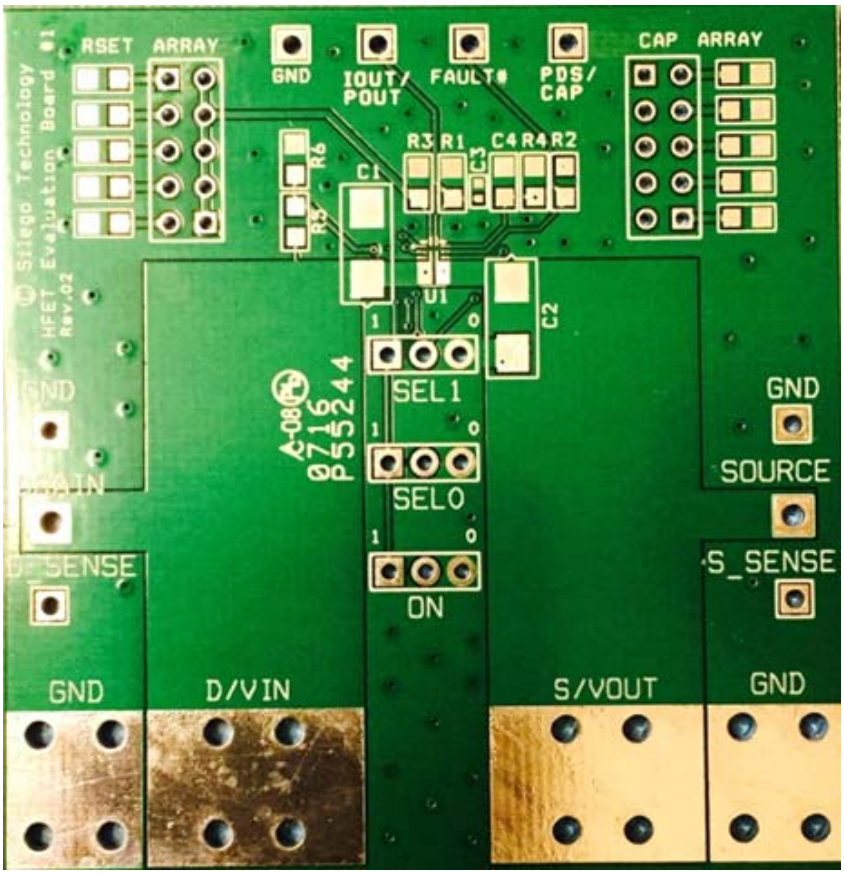


Figure 19. SLG59H1127V Evaluation Board

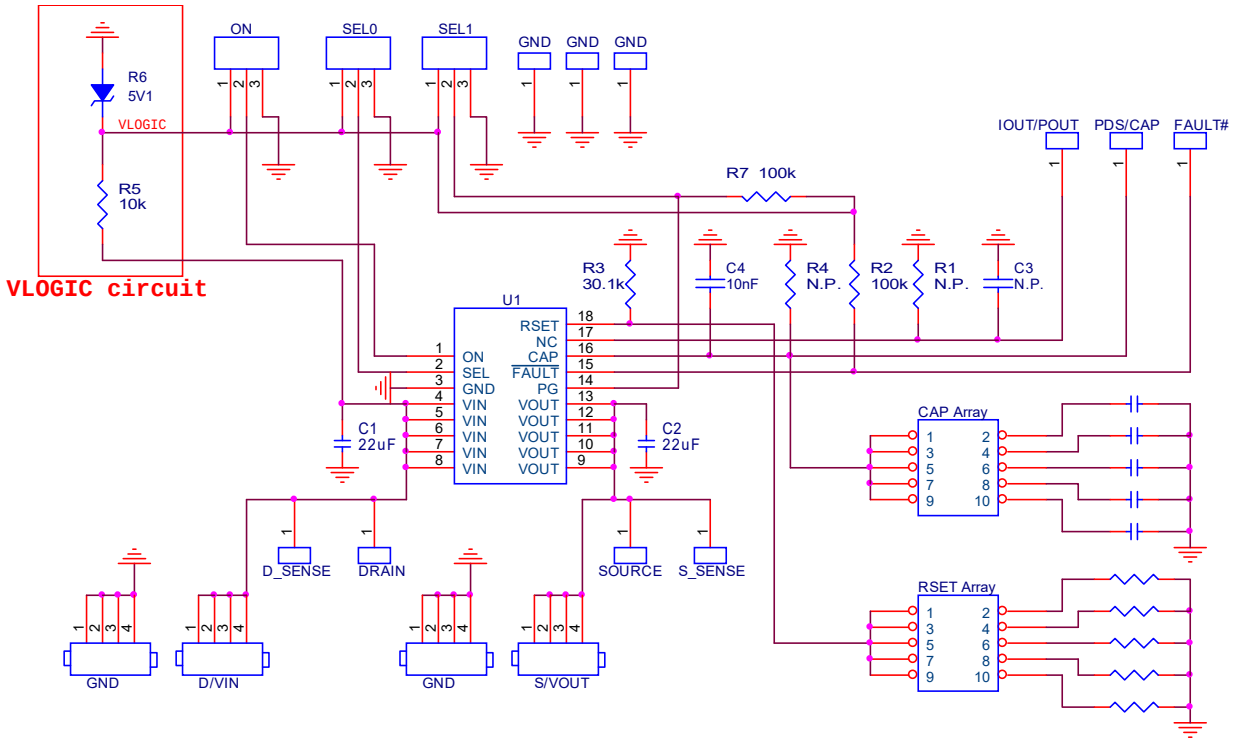


Figure 20. SLG59H1127V Evaluation Board Connection Circuit

Basic Test Setup and Connections

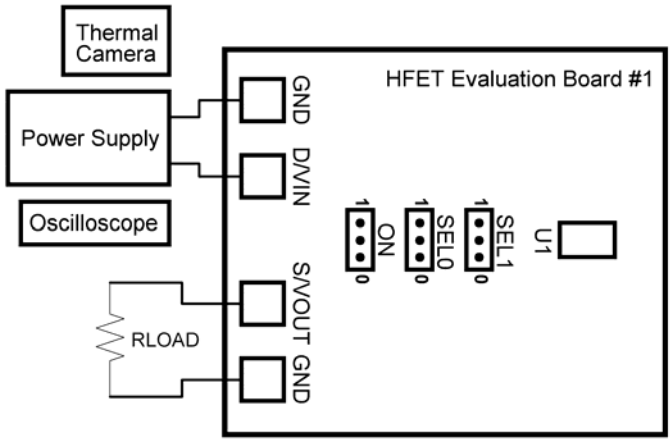
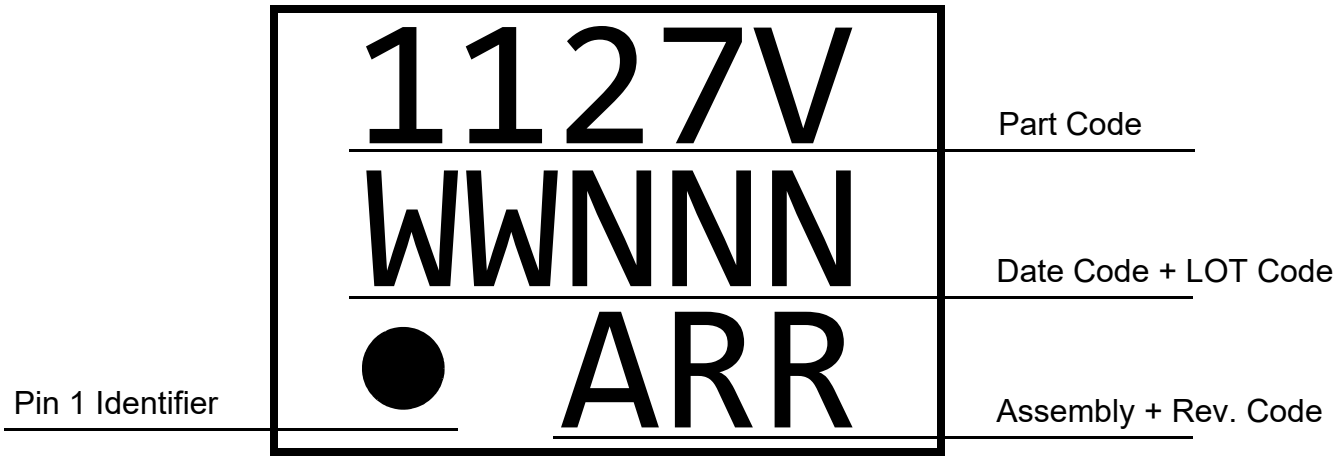


Figure 21. SLG59H1127V Evaluation Board Connection Circuit

EVB Configuration

1. Set SEL0 to GND to configure OVLO;
2. Connect oscilloscope probes to D/VIN, S/VOUT, ON, etc.;
3. Turn on Power Supply and set desired V_{IN} from 4.5 V…12 V range;
4. Toggle the ON signal High or Low to observe SLG59H1127V operation.
5. Use central SEL1 header pin for PG monitor.

Package Top Marking System Definition

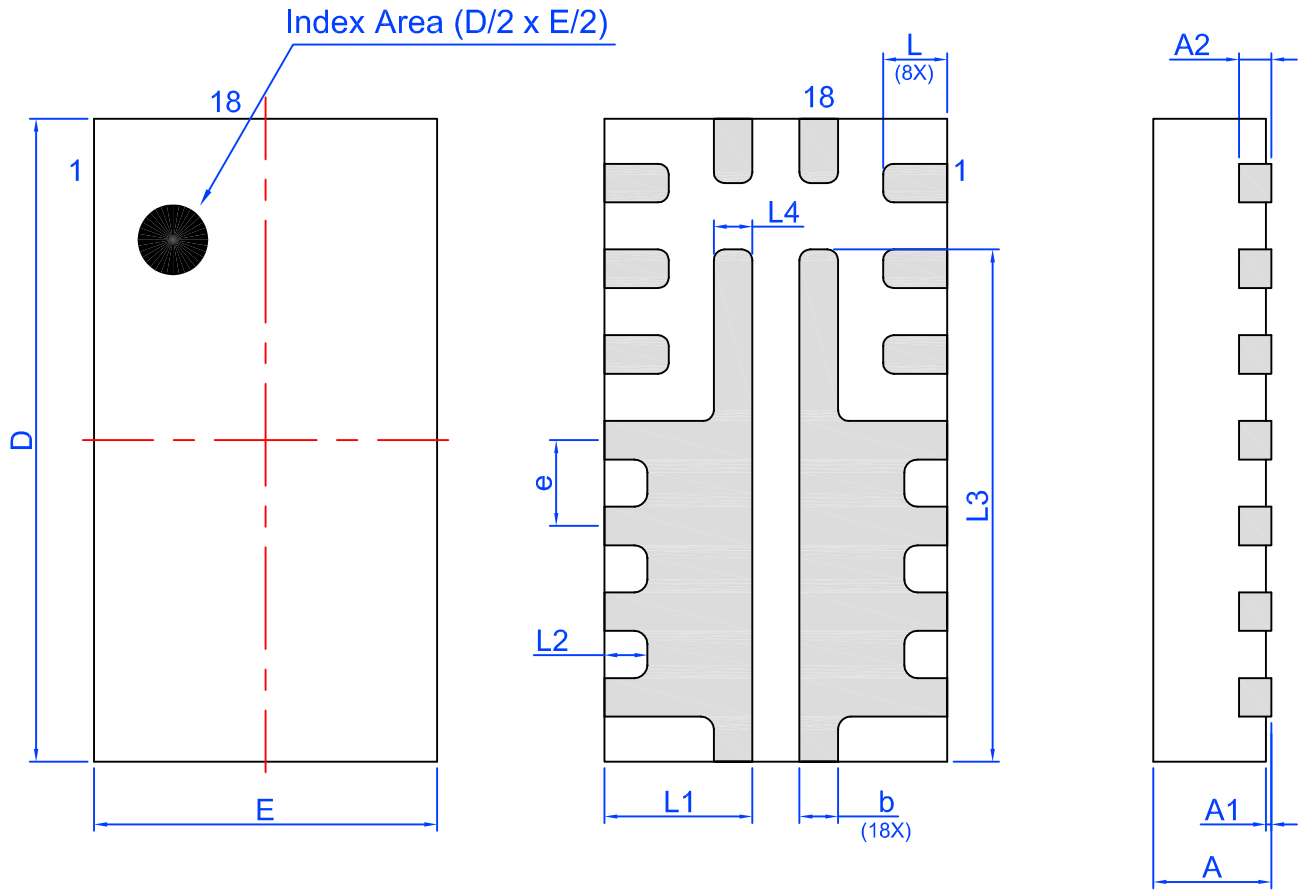


1127V - Part ID Field
WW - Date Code Field[1]
NNN - Lot Traceability Code Field[1]
A - Assembly Site Code Field [2]
RR - Part Revision Code Field[2]

Note 1: Each character in code field can be alphanumeric A-Z and 0-9
Note 2: Character in code field can be alphabetic A-Z

Package Drawing and Dimensions

18 Lead TQFN Package 1.6 x 3 mm (Fused Lead)
JEDEC MO-220, Variation WCEE

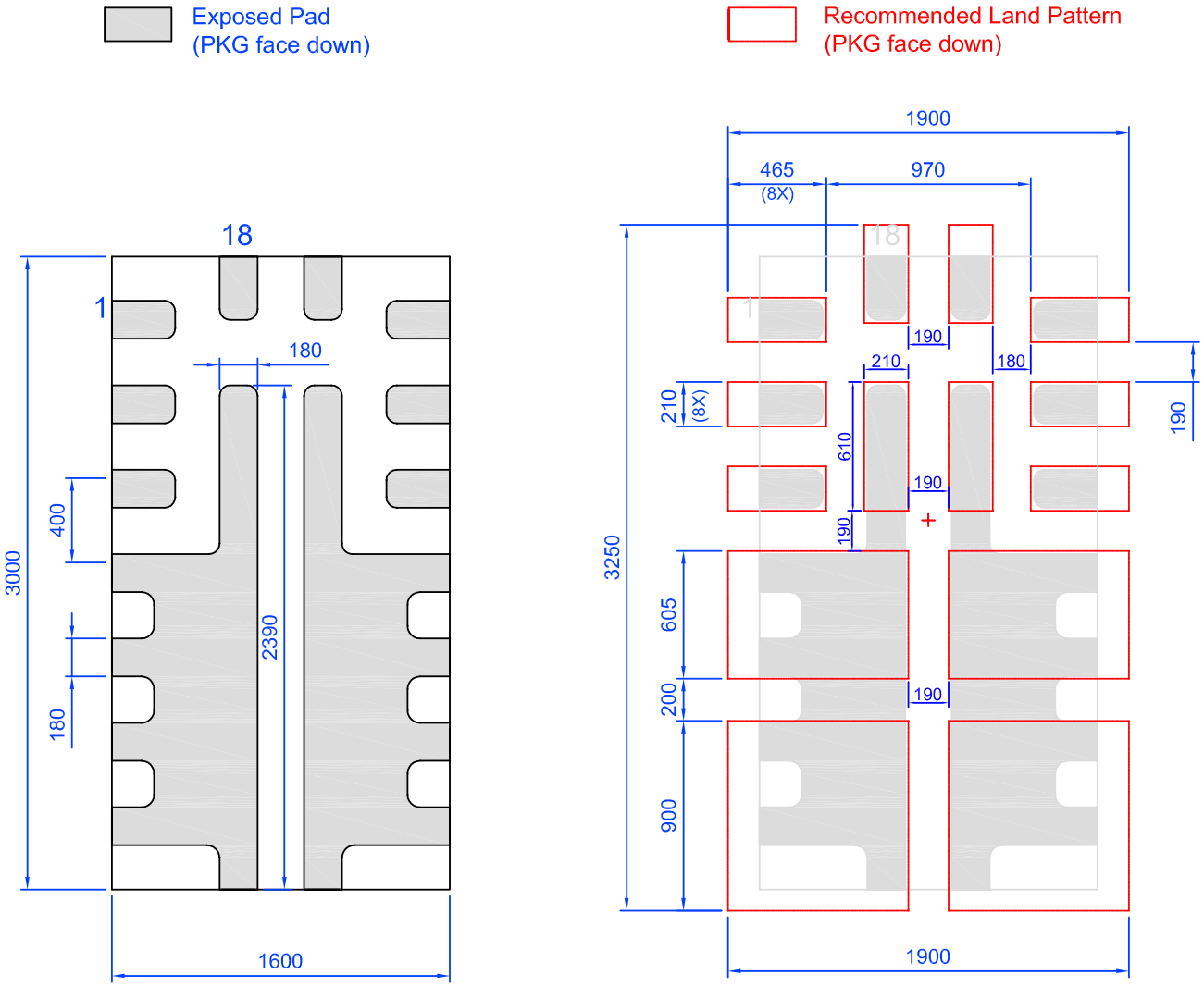


Top View BTM View Side View

Unit: mm

Symbol	Min	Nom.	Max	Symbol	Min	Nom.	Max
A	0.50	0.55	0.60	D	2.95	3.00	3.05
A1	0.005	-	0.05	E	1.55	1.60	1.65
A2	0.10	0.15	0.20	L	0.25	0.30	0.35
b	0.13	0.18	0.23	L1	0.64	0.69	0.74
e	0.40 BSC			L2	0.15	0.20	0.25
L3	2.34	2.39	2.44	L4	0.13	0.18	0.23

SLG59H1127V 18-pin STQFN PCB Landing Pattern



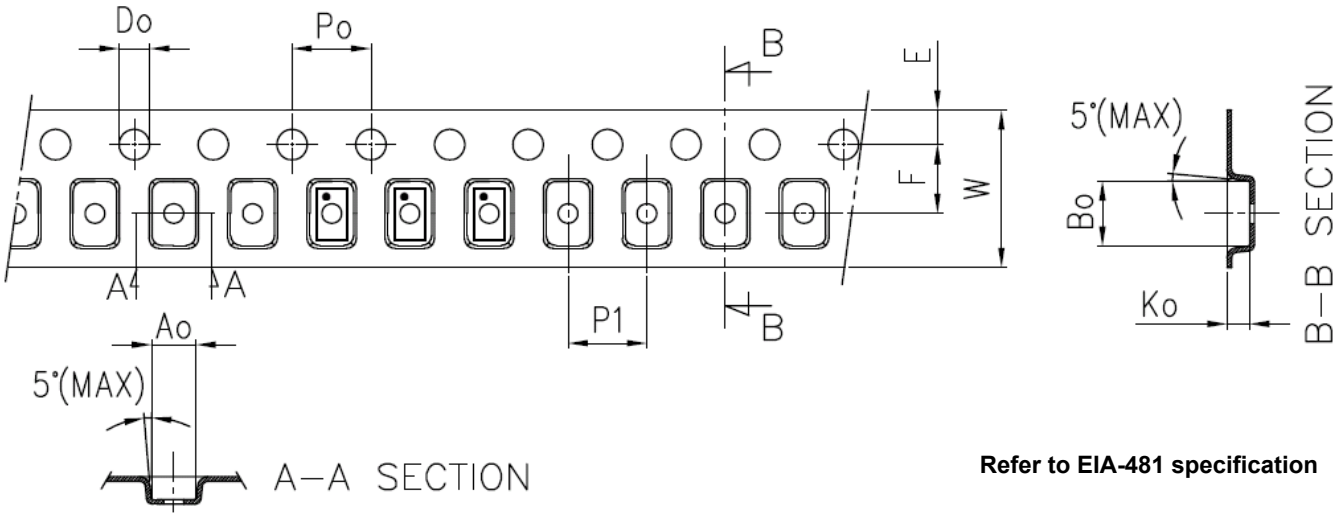
Note: All dimensions shown in micrometers (μm)

Tape and Reel Specifications

Package Type	# of Pins	Nominal Package Size [mm]	Max Units		Reel & Hub Size [mm]	Leader (min)		Trailer (min)		Tape Width [mm]	Part Pitch [mm]
			per Reel	per Box		Pockets	Length [mm]	Pockets	Length [mm]		
STQFN 18L 0.4P FC Green	18	1.6 x 3 x 0.55	3,000	3,000	178 / 60	100	400	100	400	8	4

Carrier Tape Drawing and Dimensionss

Package Type	Pocket BTM Length	Pocket BTM Width	Pocket Depth	Index Hole Pitch	Pocket Pitch	Index Hole Diameter	Index Hole to Tape Edge	Index Hole to Pocket Center	Tape Width
	A0	B0	K0	P0	P1	D0	E	F	W
STQFN 18L 0.4P FC Green	1.78	3.18	0.76	4	4	1.5	1.75	3.5	8



Refer to EIA-481 specification

Recommended Reflow Soldering Profile

Please see IPC/JEDEC J-STD-020: latest revision for reflow profile based on package volume of 2.64 mm^3 (nominal). More information can be found at www.jedec.org.

Revision History

Date	Version	Change
12/12/2018	1.02	Updated style and formatting Updated Charts and Scopeshots Fixed typos
1/16/2018	1.01	Updated RDS_{ON} vs V_{IN} and Temp Chart
2/24/2017	1.00	Production Release

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SLG59H1127V SLG59H1127V-EVB